



March 2023

Quarterly Reliability Report

Document Number DOC-113783, Revision 1



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pSemi Reliability System

The Quarterly Reliability Report is a compilation of reliability stress test results that crosses the entire product & technology family of pSemi products. Data is collected on a regular basis through the efforts of product and process qualifications, standard product monitoring and lot acceptance testing. To date, a total of **138,596 devices** have been tested in HTOL with a total of **9.12 billion equivalent device hours**. The overall failure rate for the pSemi family of products is **0.10 FIT**. (Using $E_{a} = 0.7\text{eV}$, $T_j = 55^{\circ}\text{C}$ at 60% UCL)

pSemi reliability testing standards conform to industry standard qualification procedures as detailed in the JEDEC guidelines. In addition, where clear guidelines have not been established yet, pSemi has developed stringent reliability requirements to ensure consistent high reliability performance.

pSemi makes use of accelerated life testing results, along with thermal acceleration factors in the prediction of failure rates. High Temperature Operating Life (HTOL) stress testing is performed at accelerated voltage and temperature conditions which are based Jedec-JESD22-A108 standards. Resulting data collected from HTOL tests is de-rated to a typical use operating junction temperature (T_j) of 55°C . Early Life Failure Rate (ELFR) is derived after 48-hr performance.

pSemi conducts an ongoing product reliability monitoring program to evaluate sample products from high volume, major product families on a quarterly basis. The reliability monitoring process is a continuously improving system within pSemi as we strive for superior product knowledge and performance.

pSemi performs the majority of Reliability testing using an ISO17025 certified test laboratories located in San Jose, CA. Regular auditing of the laboratory is performed to ensure compliance to ISO standards.

Failure Rate Calculation

Acceleration Factor (AF)

For a given failure mechanism, acceleration factor (AF), is the ratio of the time it takes for a certain fraction of the population to fail, following application of one stress or use condition, to the corresponding time at a more severe stress or use condition.

The industry uses the thermal acceleration model formula based on Arrhenius equation noted below:

$$AF(T_{use}, T_{stress}) := e^{\frac{E_{aa}}{k_B} \cdot \left(\frac{1}{T_{use}} - \frac{1}{T_{stress}} \right)}$$

where:

$E_{aa} := 0.7 \text{ eV}$, is the Apparent Activation Energy

$e = 2.718$, is the base of natural logarithm

$k_B := 8.62 \cdot 10^{-5} \frac{\text{eV}}{\text{K}}$, is the Boltzmann constant

T_{use} & T_{stress} , are the use and stress test temperatures, respectively, in Kelvin

Sample Calculation

Find the Acceleration Factor (AF) with the following conditions.

(a) $T_{use} := 55 \text{ }^{\circ}\text{C}$ and $T_{stress} := 125 \text{ }^{\circ}\text{C}$

$$AF(T_{use}, T_{stress}) = 77.5$$

(b) $T_{use} := 55 \text{ }^{\circ}\text{C}$ and $T_{stress} := 150 \text{ }^{\circ}\text{C}$

$$AF(T_{use}, T_{stress}) = 258.7$$

Failure Rate Calculation (continued)

Failure in Time Calculation

Mean time to failure (M.T.T.F.) is defined as the average time it takes for a failure to occur. Failure in Time (F.I.T.) is the number of units predicted to fail in a billion ($1e^9$) device hours at a specified temperature. After the life test is completed and accelerated device hour data is calculated, the failure rate is estimated using the Chi-Square approximation (χ^2) as follows:

$$FIT = \left(\frac{\chi^{2(2r+2)}}{2 * EDH} \right) * 1e^9$$

where:

χ^2 = chi square function

r = number of failures

EDH = equivalent device hours (units tested x test hours x AF)

Sample Calculation

Given: Units Tested (Sample Size) = 231 devices
 Test temperature = 150°C
 Test duration = 500 hours
 Failures = 0

$EDH = (231 \times 500 \times 259.2) = 2.99E+7$ equivalent device hours

χ^2 @ 60% confidence level and 0 failures = 1.83

FIT (60% confidence level) = $[1.83 / (2 \times 2.99E+7)] \times 1.0E+9 = \underline{30.6 FIT}$

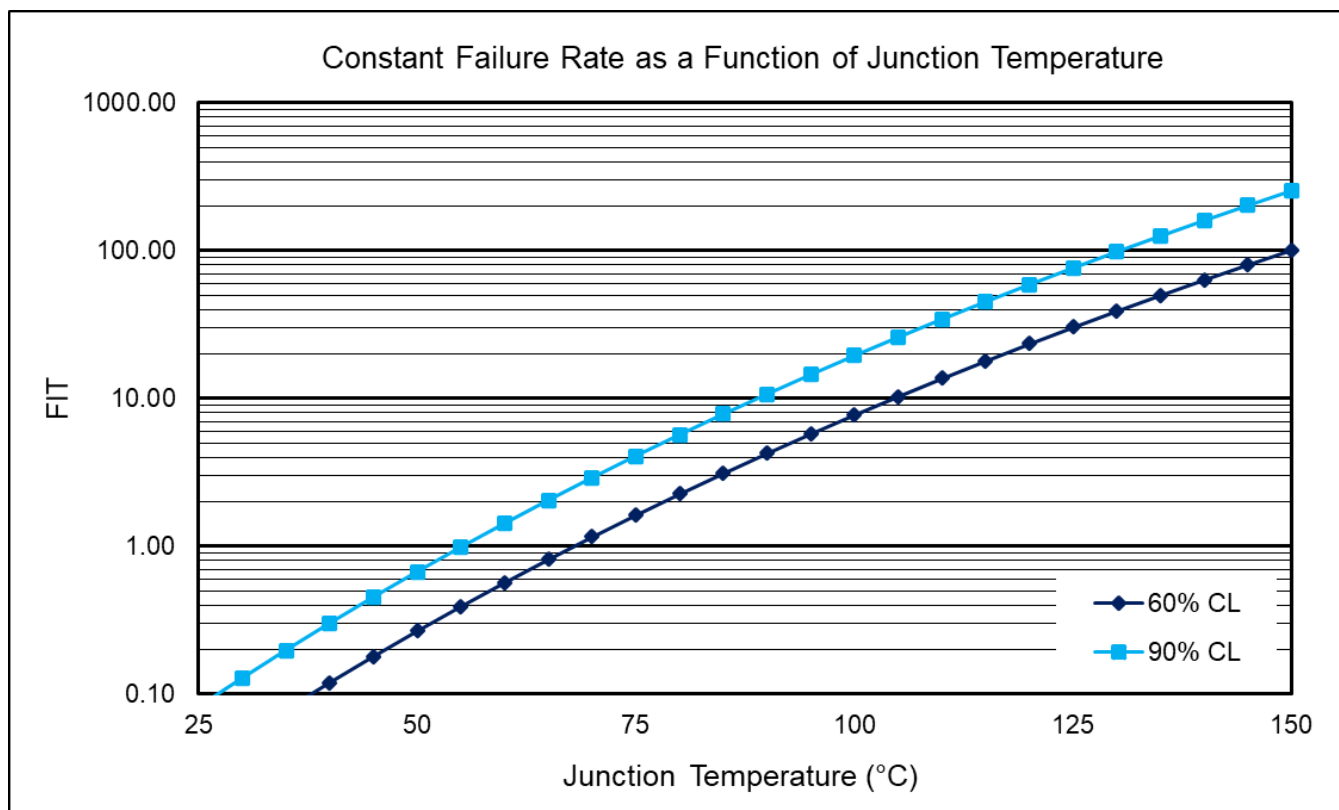
The background of the slide features a repeating pattern of light gray circuit board traces. These traces form a complex, interconnected web of lines and small circular nodes, resembling a printed circuit board (PCB) layout. The pattern is consistent across the entire background, with a slightly higher density of traces in the top and bottom sections, framing the central text area.

Technology Classification

UltraCMOS® 2 Process Technology

Generation : 500 nm CMOS Silicon Epi Process (U500E)
 Units Tested : 35,458
 Product Family : DC-DC, DSA, MXR, PLL, PSR, Switch

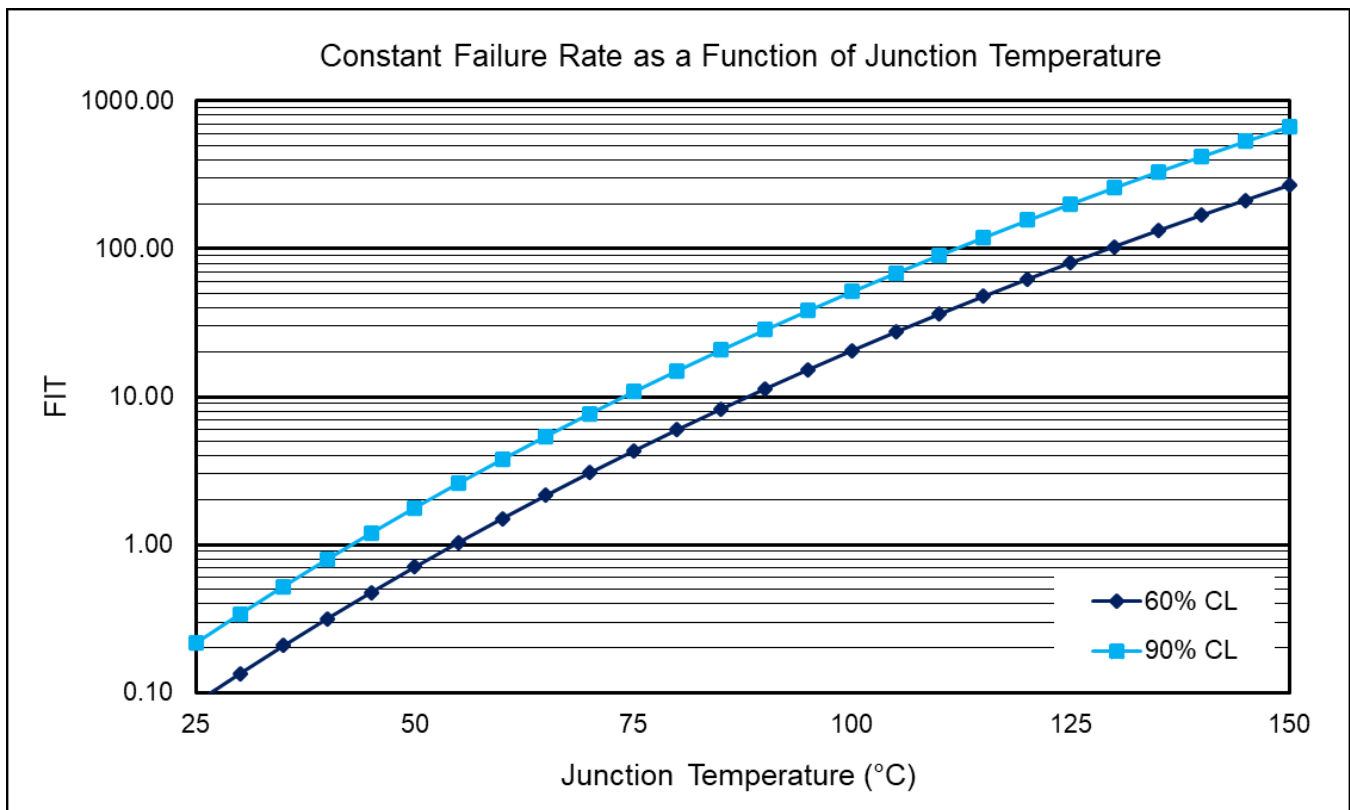
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	2.85E+08	3.2	3.11E+08
Constant (Random)	2.34E+09	0.4	2.55E+09



UltraCMOS® 3.5 Process Technology

Generation : 350 nm CMOS Silicon Epi Process (U350E)
 Units Tested : 9,372
 Product Family : DSA, DTC, Switch

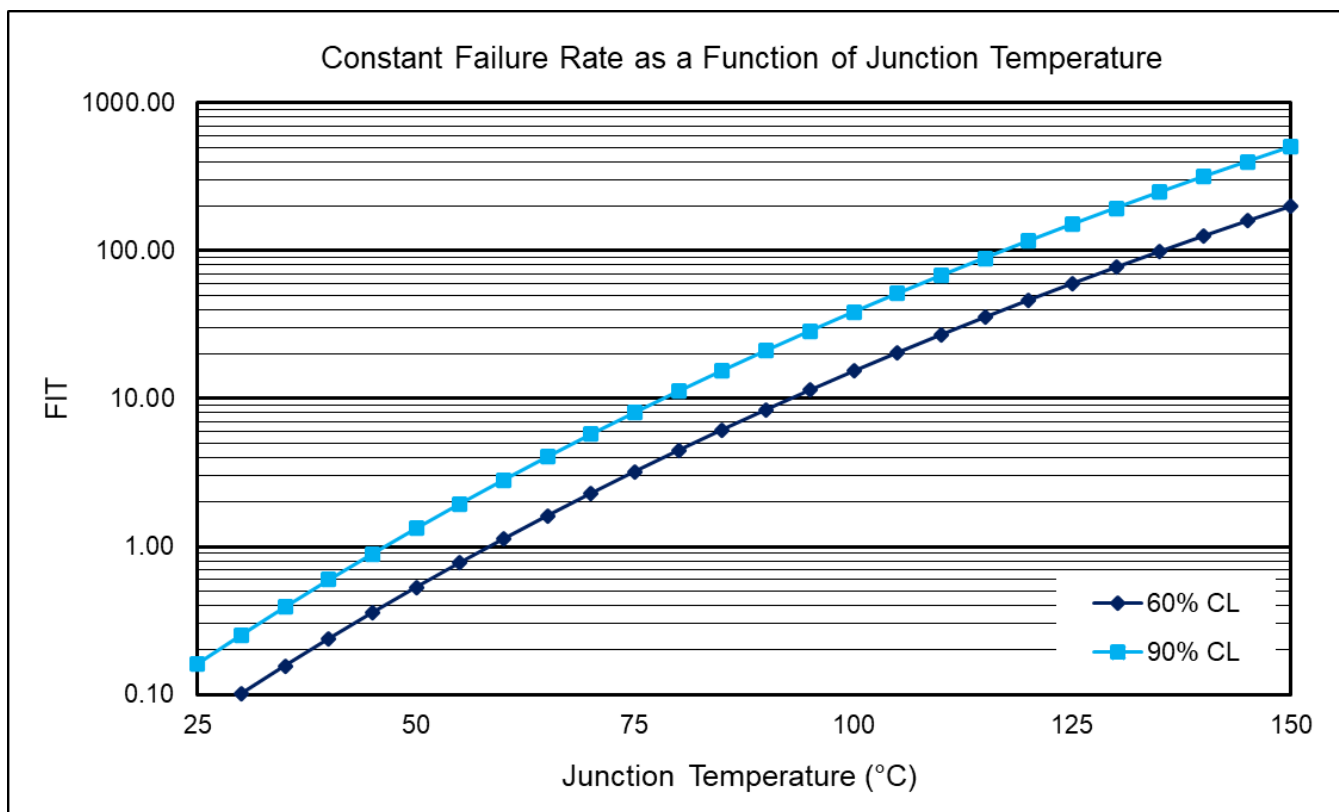
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	1.13E+08	8.1	1.23E+08
Constant (Random)	8.83E+08	1.0	9.63E+08



UltraCMOS[®] 5 Process Technology

Generation : 350 nm CMOS Bonded Silicon Process (U350B)
 Units Tested : 9,216
 Product Family : DSA, DTC, LMTR, MPAC, PLL, PSH, Switch

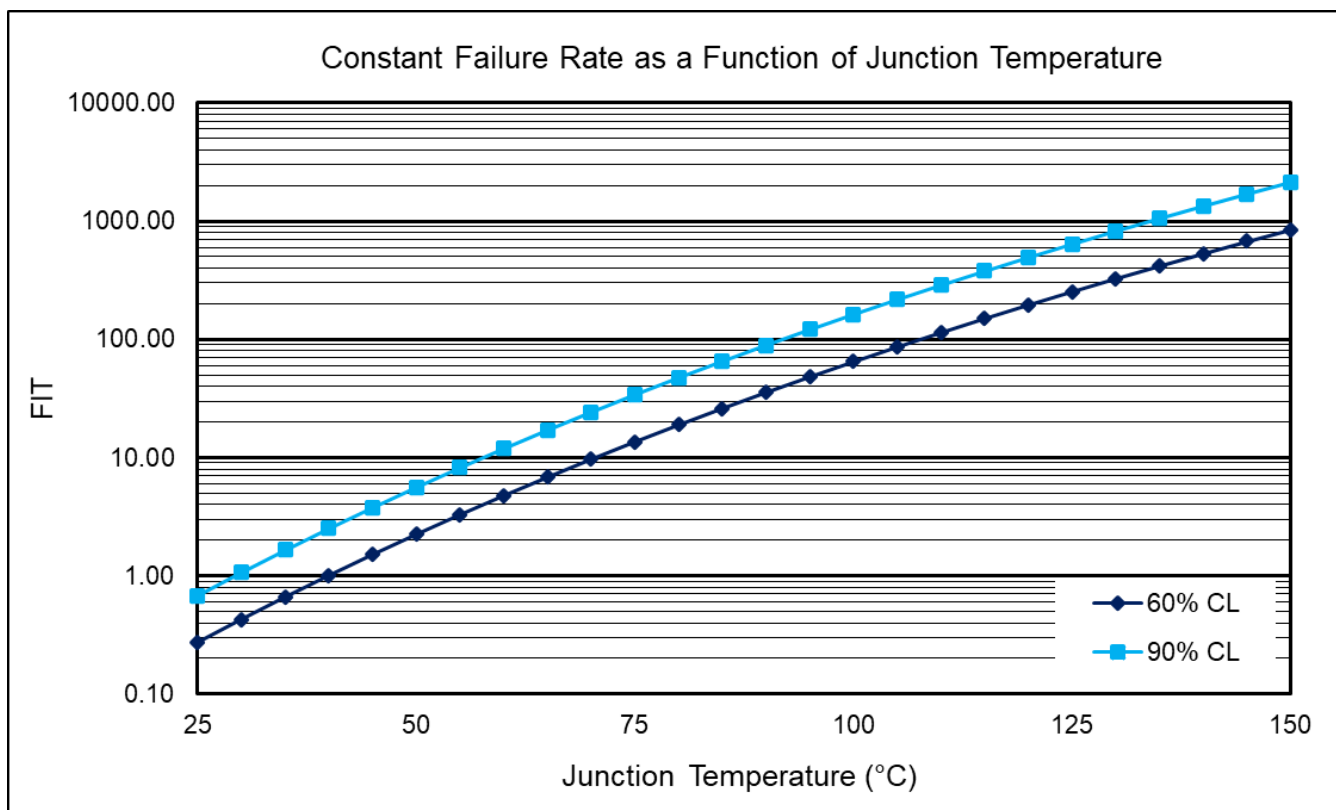
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	1.12E+08	8.2	1.23E+08
Constant (Random)	1.18E+09	0.8	1.29E+09



UltraCMOS[®] 6 Process Technology

Generation : 250 nm CMOS Silicon Epi Process (U250E2)
 Units Tested : 2,271
 Product Family : Switch

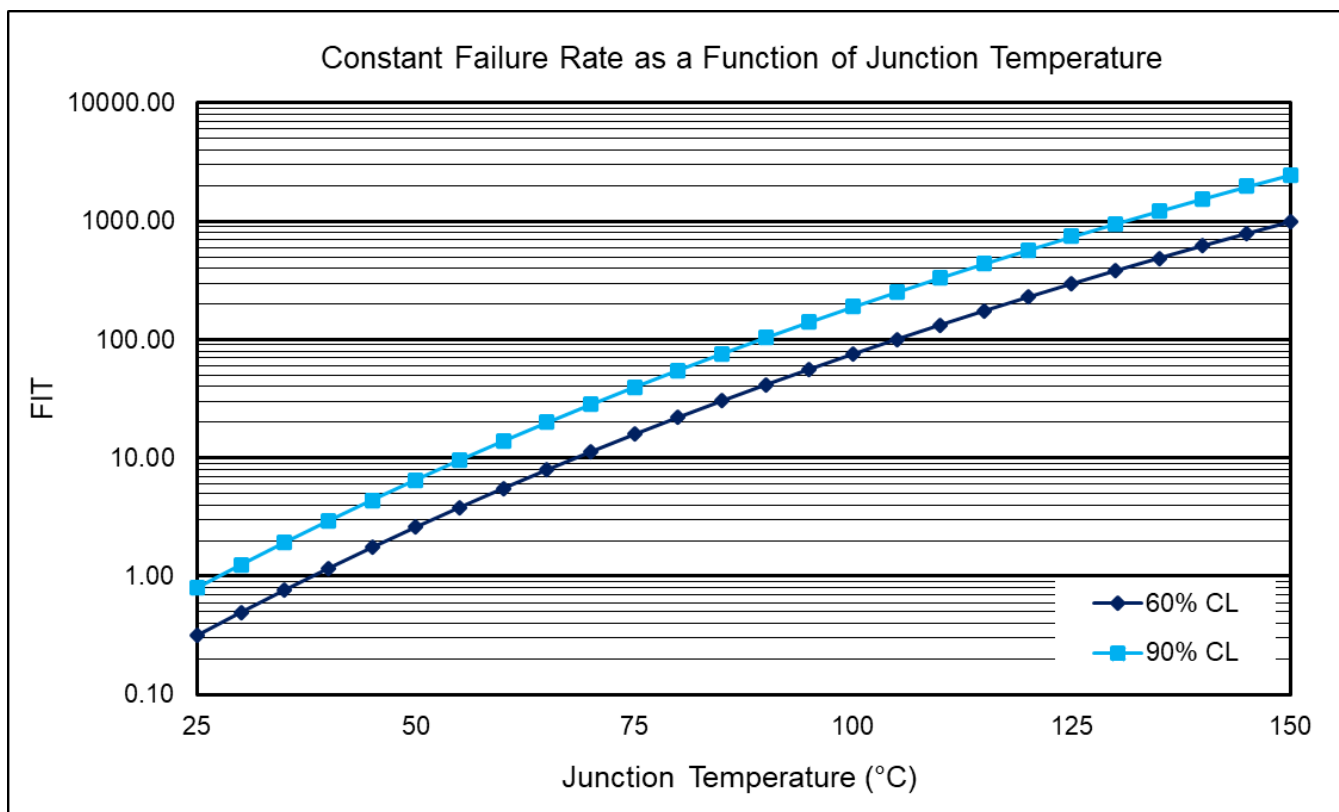
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	2.71E+07	33.8	2.96E+07
Constant (Random)	2.79E+08	3.3	3.05E+08



UltraCMOS® 6.5 Process Technology

Generation : 250 nm CMOS Silicon Epi Process (U250E4)
 Units Tested : 1,914
 Product Family : Driver, DSA, Switch

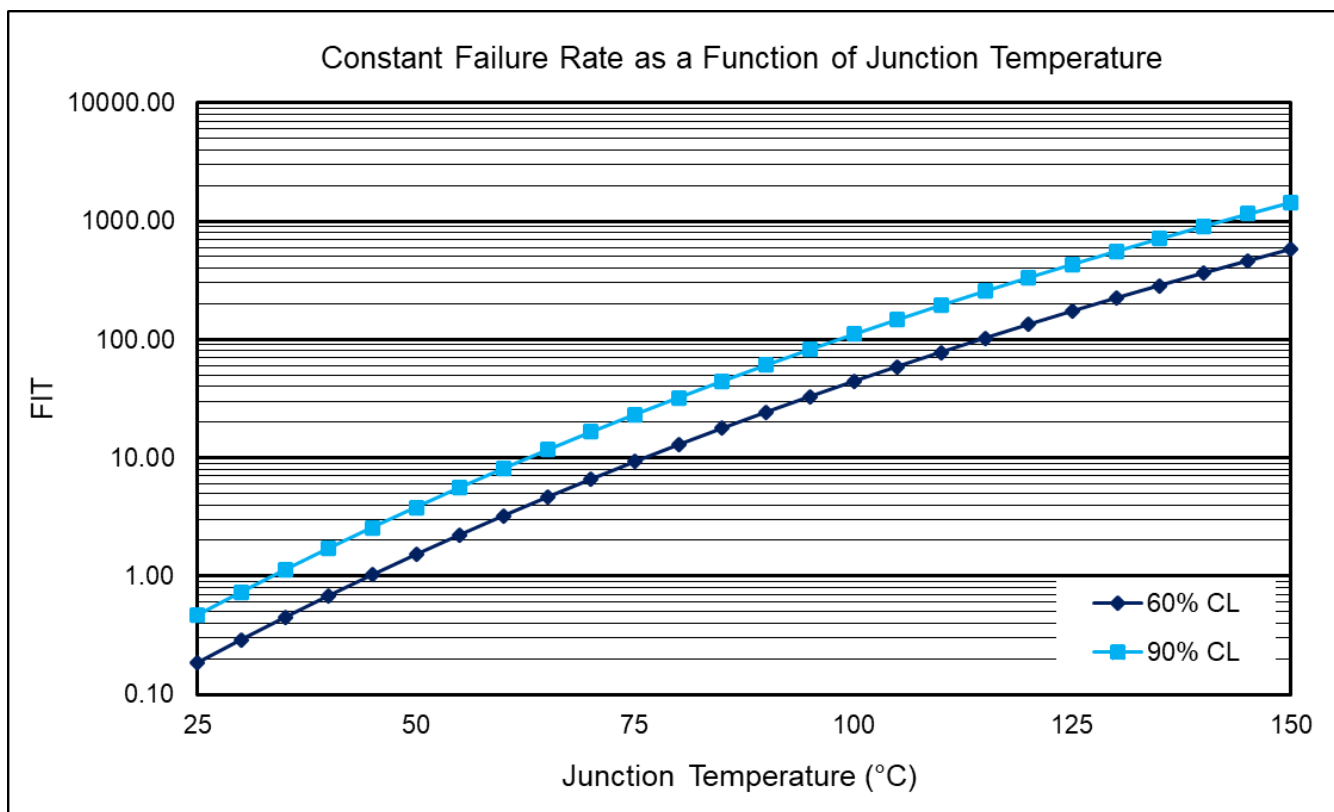
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	1.94E+07	47.3	2.11E+07
Constant (Random)	2.40E+08	3.8	2.62E+08



UltraCMOS[®] 8 Process Technology

Generation : 250 nm CMOS Bonded Silicon Process (U250B)
 Units Tested : 3,205
 Product Family : Driver, DSA, DTC, LMTR, MPAC, MXR, PSR, Switch

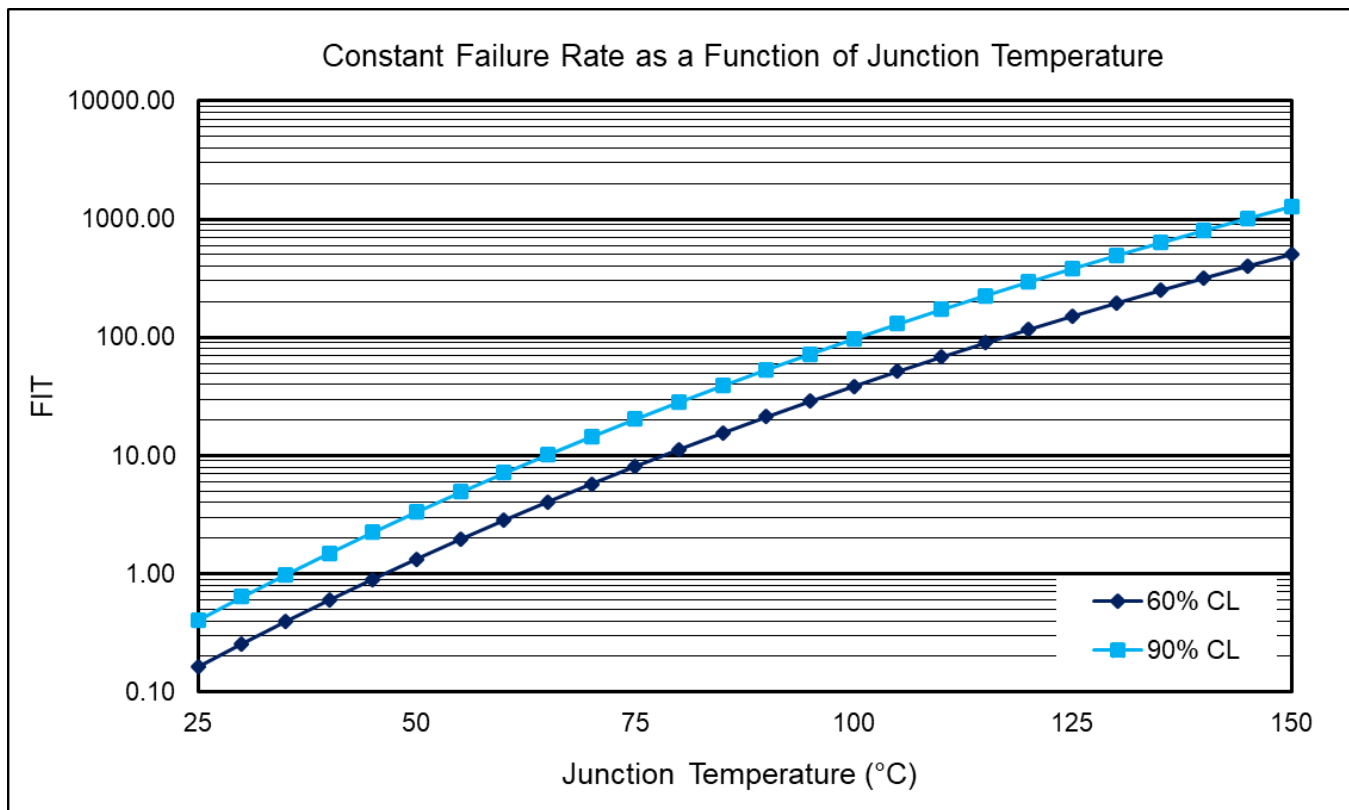
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	3.79E+07	24.2	4.13E+07
Constant (Random)	4.11E+08	2.2	4.48E+08



UltraCMOS® 10 Process Technology

Generation : 130nm CMOS Silicon-On-Insulator in 200mm wafer(U130S1)
 Units Tested : 3,869
 Product Family : Switch

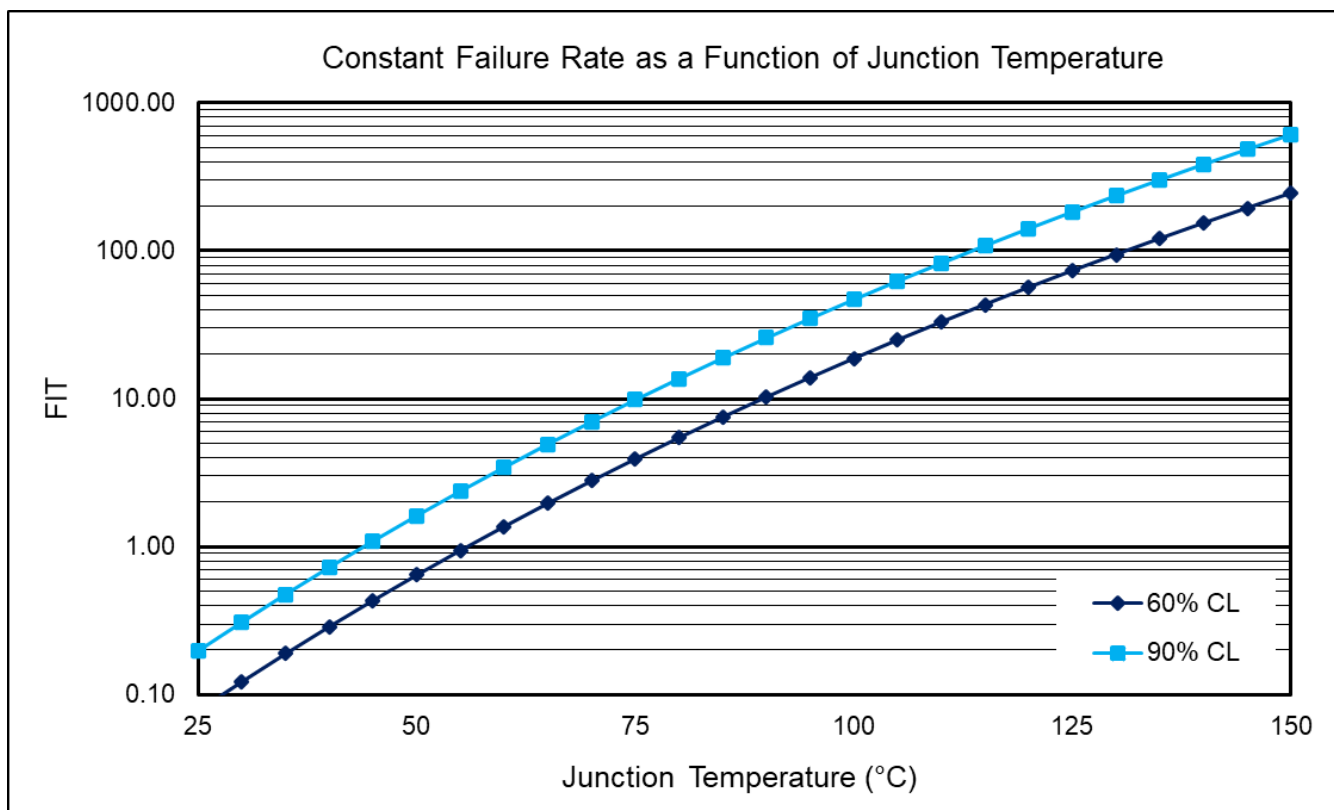
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	4.14E+07	22.1	4.52E+07
Constant (Random)	4.68E+08	2.0	5.10E+08



UltraCMOS[®] 11 Process Technology

Generation : 130nm CMOS Silicon-On-Insulator in 300mm wafer (U130S2)
 Units Tested : 12,888
 Product Family : Amplifier, DC-DC, Switch

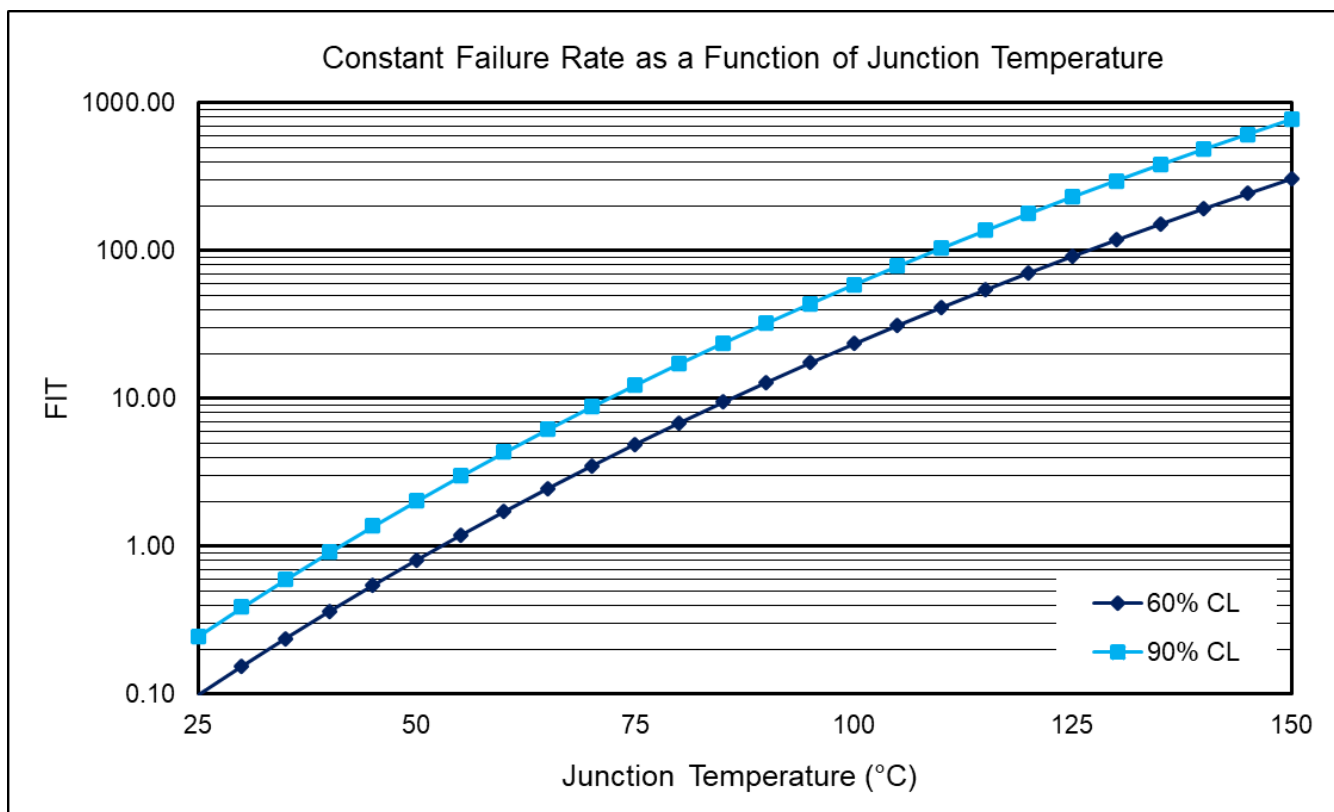
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	7.77E+07	11.8	8.48E+07
Constant (Random)	9.69E+08	0.9	1.06E+09



UltraCMOS[®] 12 Process Technology

Generation : 65nm CMOS Silicon-On-Insulator in 300mm wafer (U130S3)
 Units Tested : 17,100
 Product Family : Amplifier, DSA, PAC, Switch

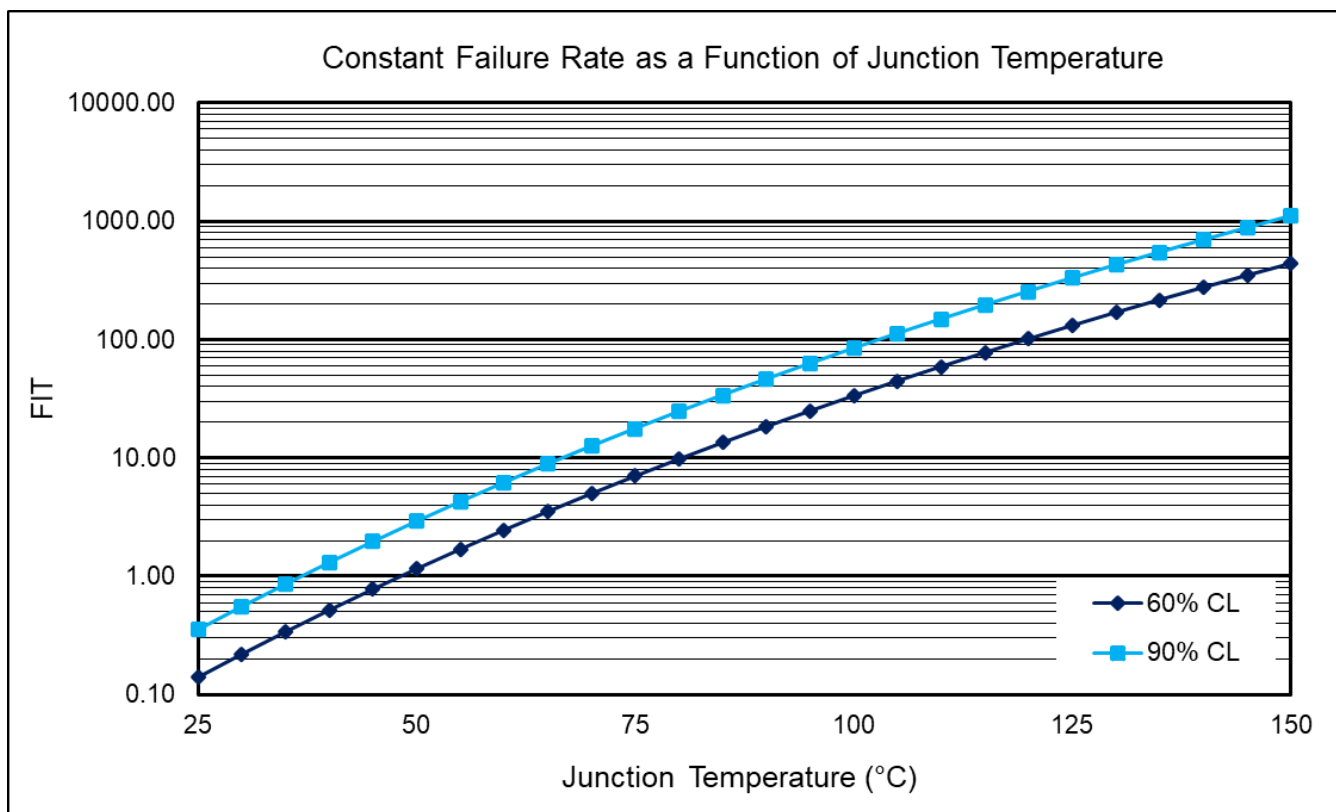
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	8.69E+07	10.5	9.49E+07
Constant (Random)	7.72E+08	1.2	8.43E+08



UltraCMOS® 12A Process Technology

Generation : 65nm CMOS Silicon-On-Insulator in 300mm wafer (U130S4)
 Units Tested : 8,522
 Product Family : Amplifier, mmWave, Switch

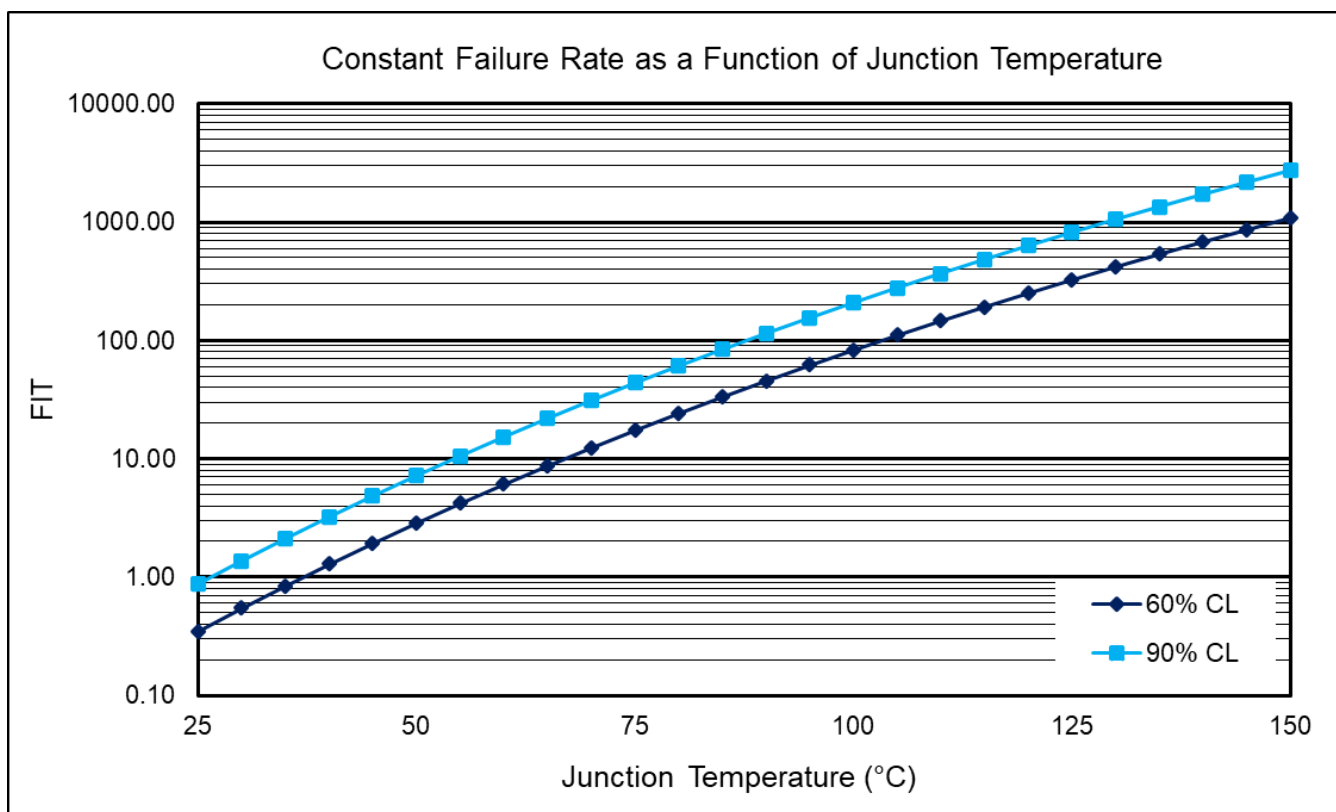
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	3.64E+07	25.2	3.97E+07
Constant (Random)	5.40E+08	1.7	5.89E+08



UltraCMOS® 13 Process Technology

Generation : 65nm CMOS Silicon-On-Insulator in 300mm wafer (U130S4)
 Units Tested : 5,778
 Product Family : Amplifier, Switch

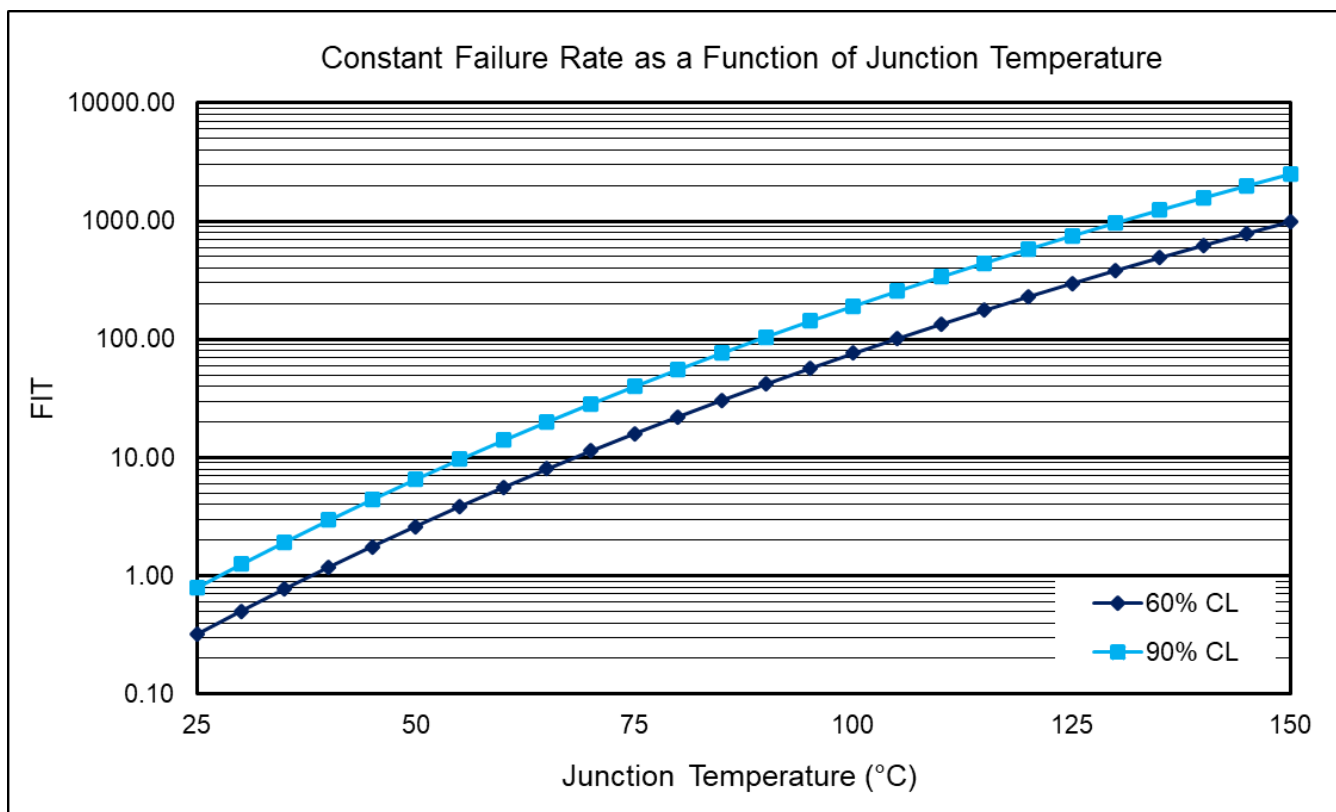
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	2.15E+07	42.6	2.35E+07
Constant (Random)	2.18E+08	4.2	2.38E+08



UltraCMOS[®] 13S Process Technology

Generation : 65nm CMOS Silicon-On-Insulator in 300mm wafer (U130S4)
 Units Tested : 13,483
 Product Family : Amplifier, Switch

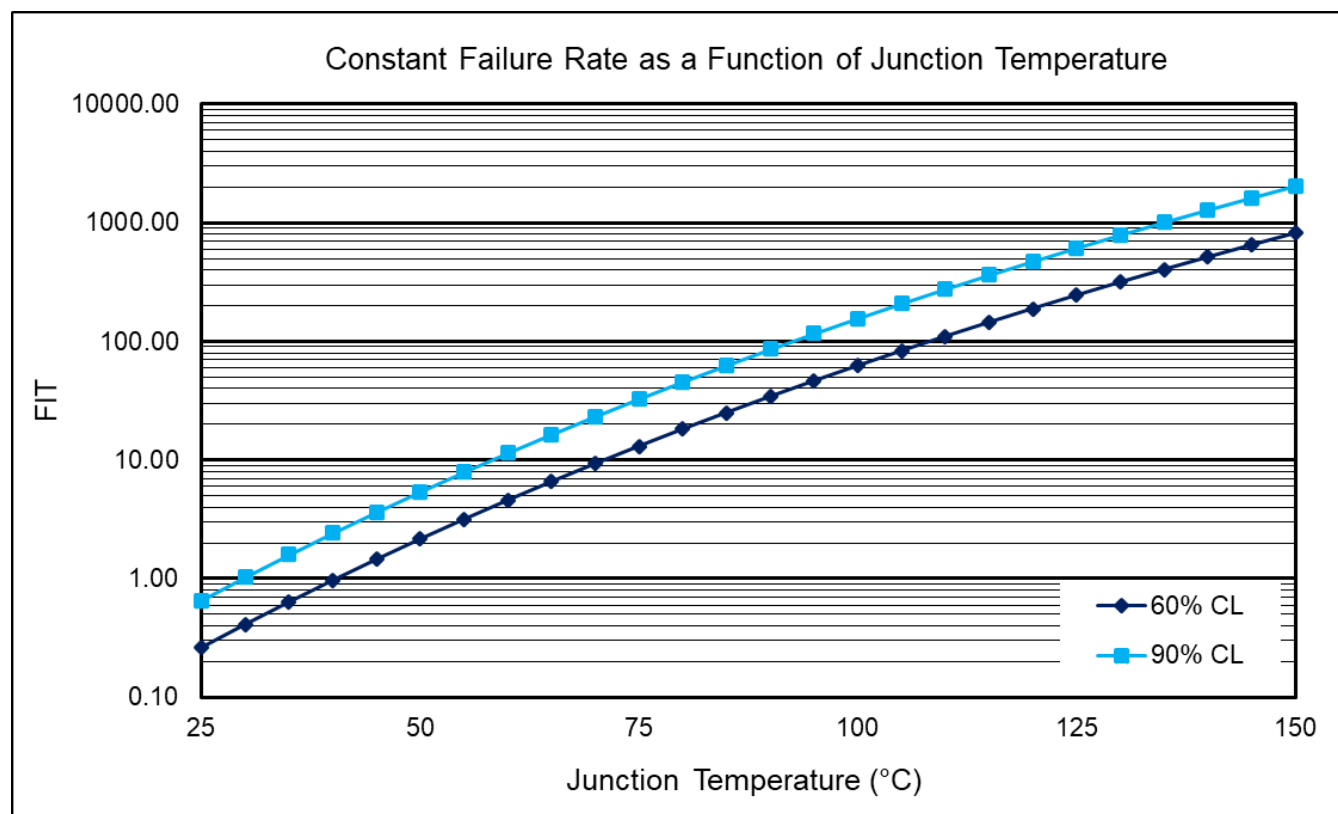
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	4.83E+07	19.0	5.27E+07
Constant (Random)	2.38E+08	3.9	2.60E+08



UltraCMOS[®] 13SA Process Technology

Generation : 65nm CMOS Silicon-On-Insulator in 300mm wafer (U130S4)
 Units Tested : 10,930
 Product Family : Switch

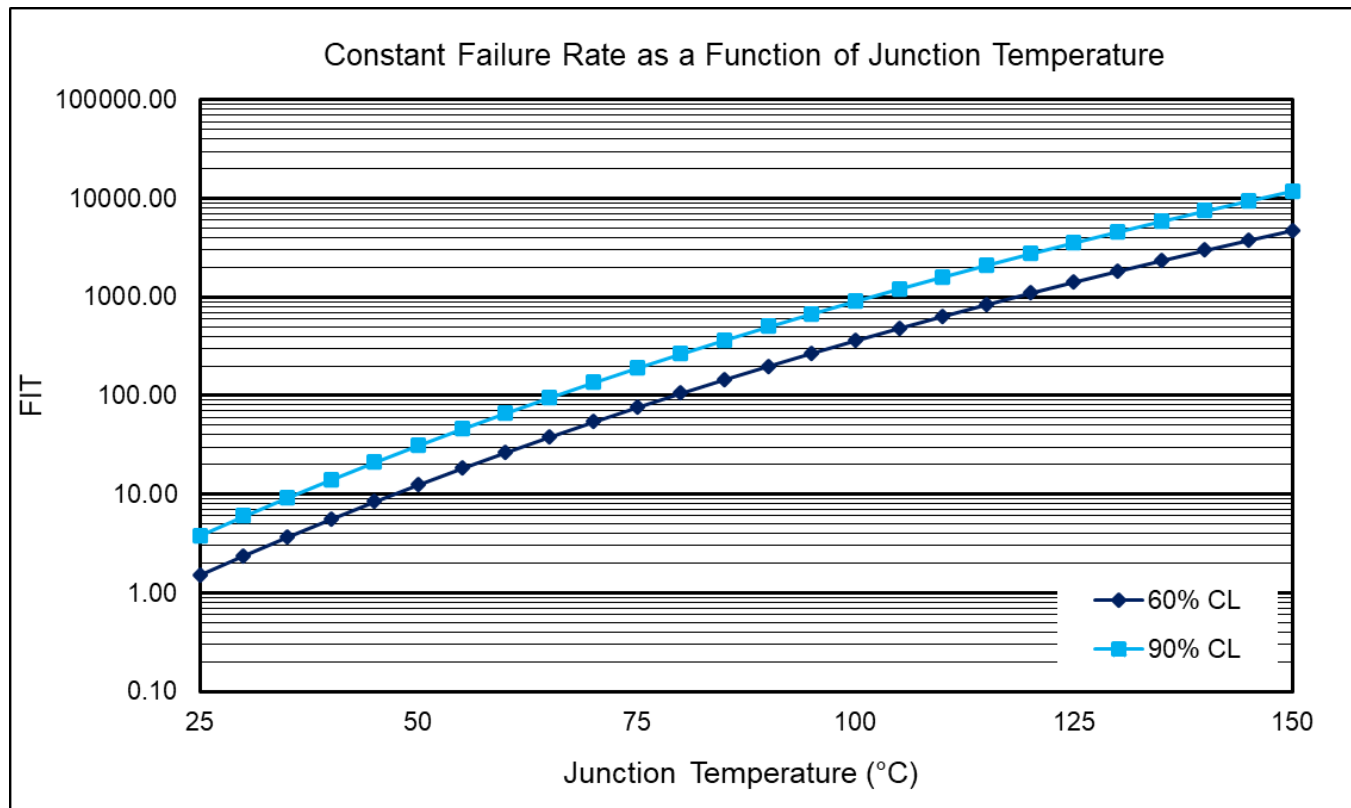
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	3.82E+07	24.0	4.17E+07
Constant (Random)	2.90E+08	3.2	3.17E+08



UltraCMOS[®] 14 Process Technology

Generation : 65nm CMOS Silicon-On-Insulator in 300mm wafer (U14UD)
 Units Tested : 1,479
 Product Family : Switch

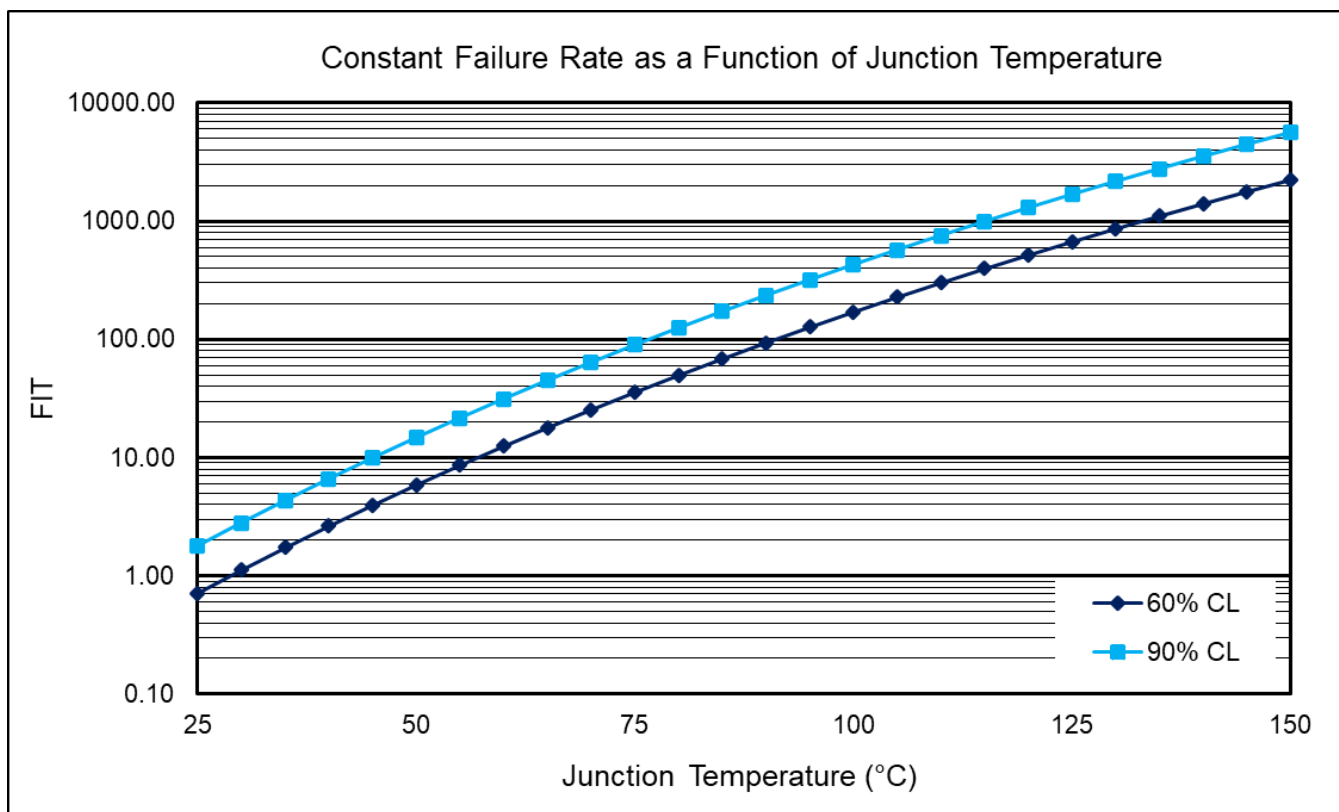
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	3.07E+06	298.8	3.35E+06
Constant (Random)	4.98E+07	18.4	5.44E+07



BCD GEN II Process Technology

Generation : 180nm BCD Gen 2 Process
 Units Tested : 1,370
 Product Family : DC-DC

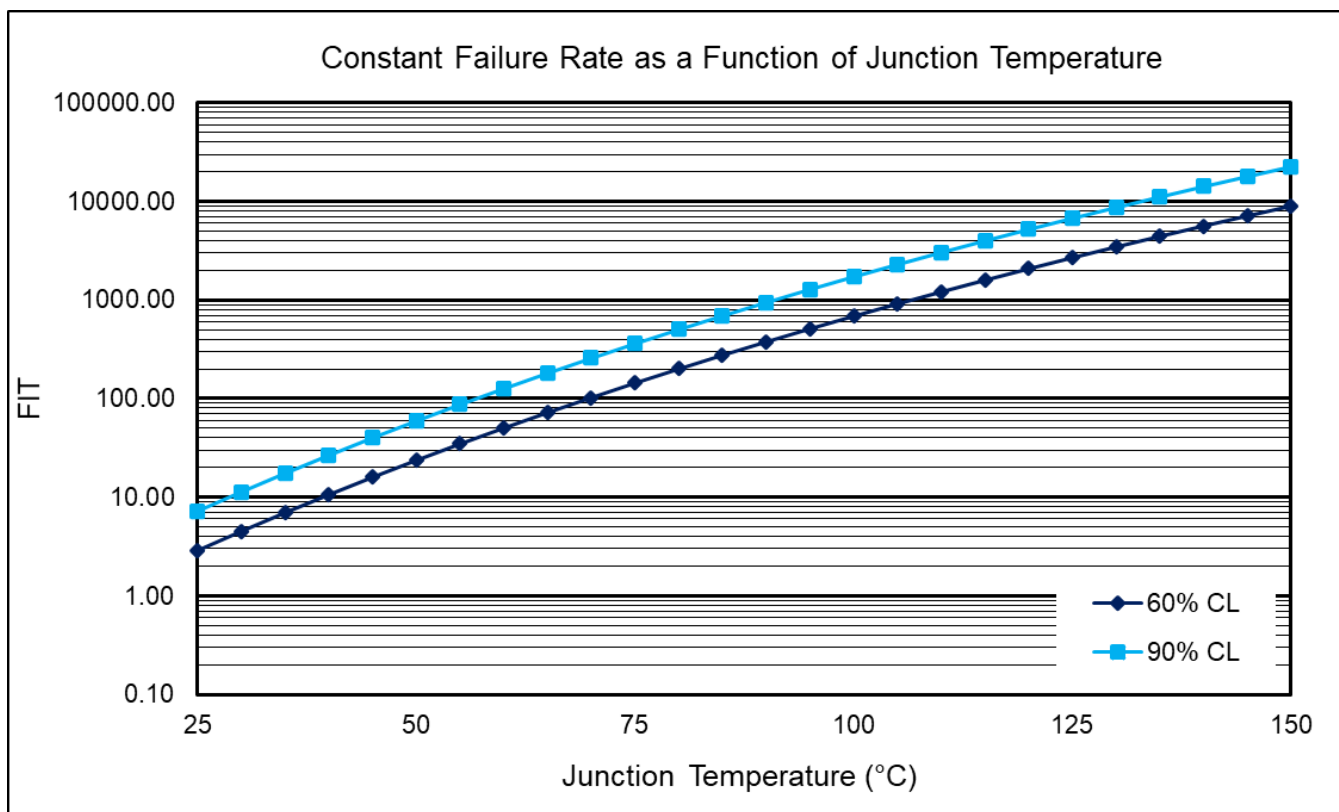
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	5.10E+06	179.7	5.56E+06
Constant (Random)	1.06E+08	8.6	1.16E+08



BCD GEN III Process Technology

Generation : 180nm BCD Gen 3 Process
 Units Tested : 340
 Product Family : DC-DC

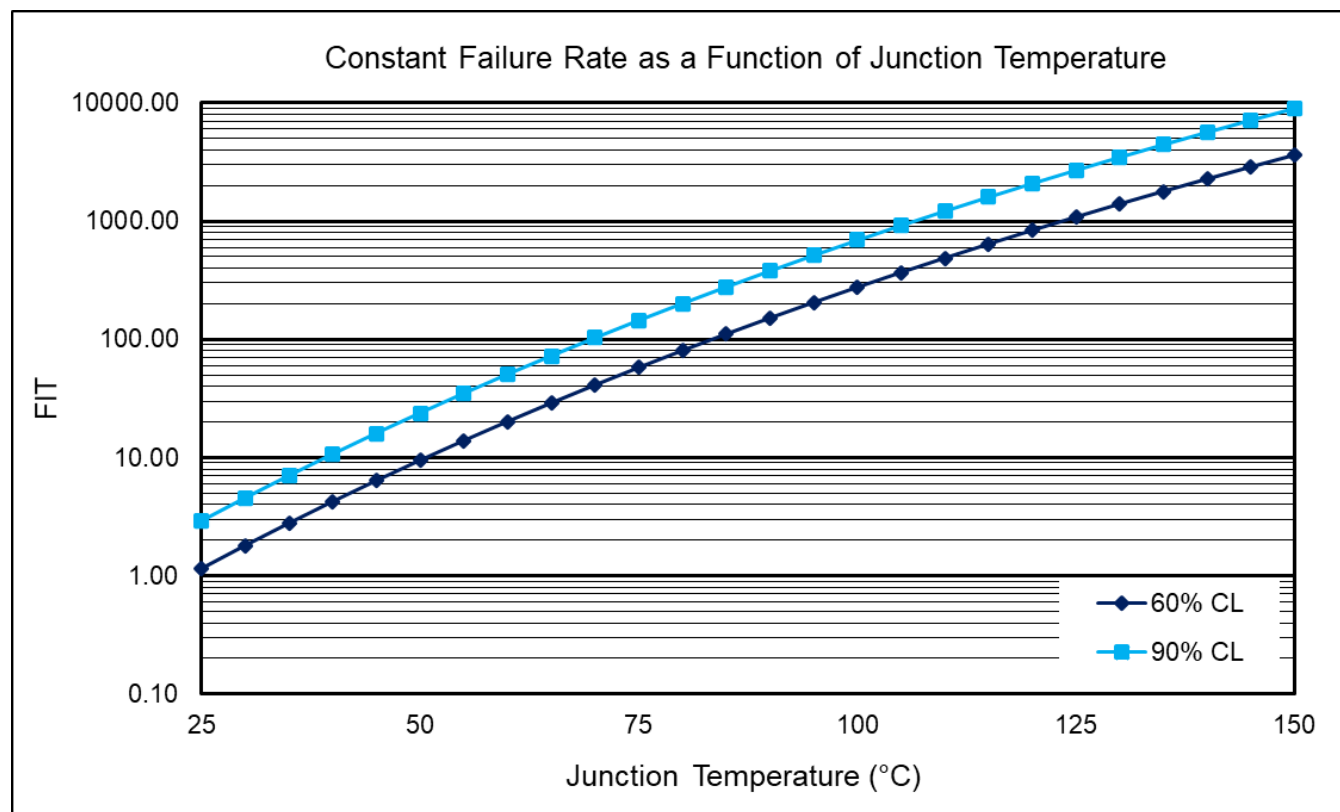
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	1.27E+06	724.1	1.38E+06
Constant (Random)	2.64E+07	34.8	2.88E+07



BCDLite Process Technology

Generation : 130nm BCDLite Process
 Units Tested : 786
 Product Family : DC-DC

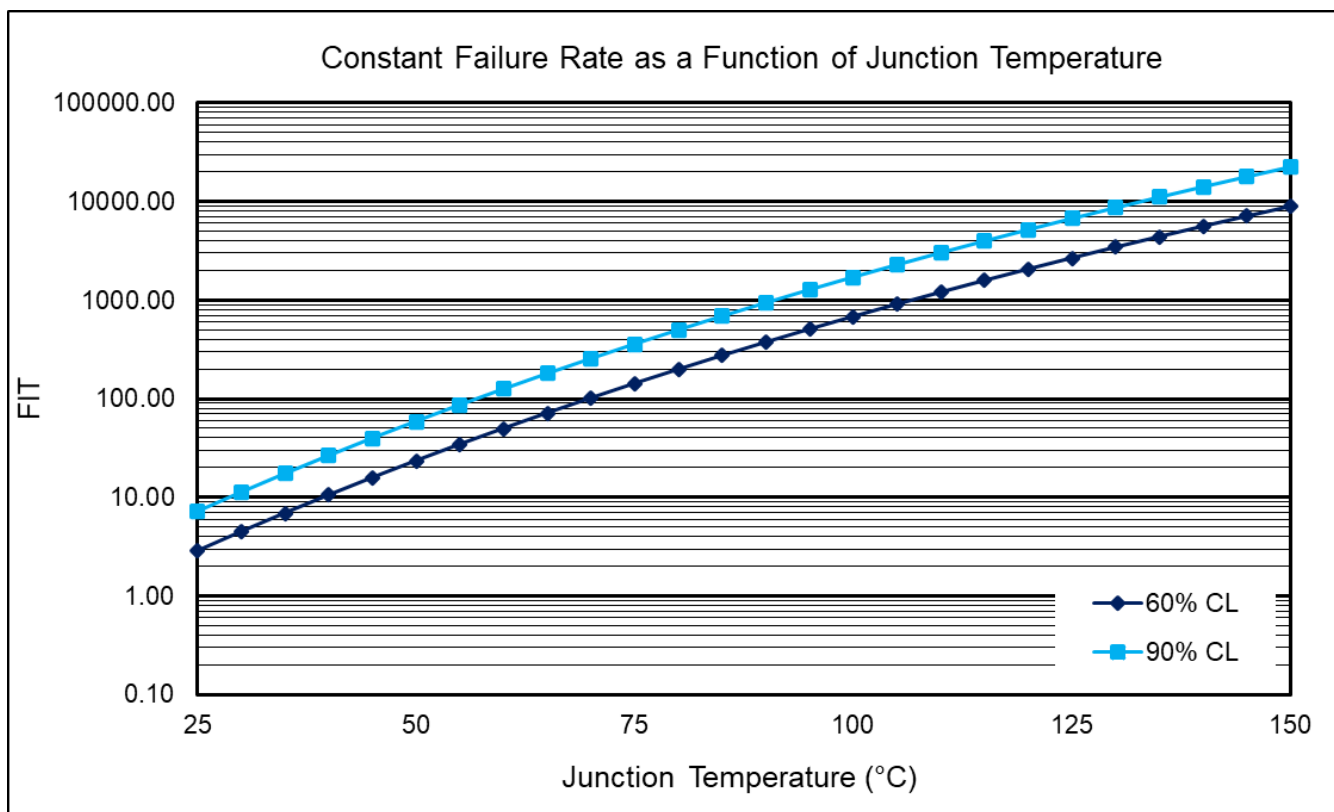
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	4.82E+06	190.0	5.26E+06
Constant (Random)	6.59E+07	13.9	7.19E+07



55LPx Process Technology

Generation : 55nm 300mm wafer (C055C1E6)
 Units Tested : 343
 Product Family : ASIC

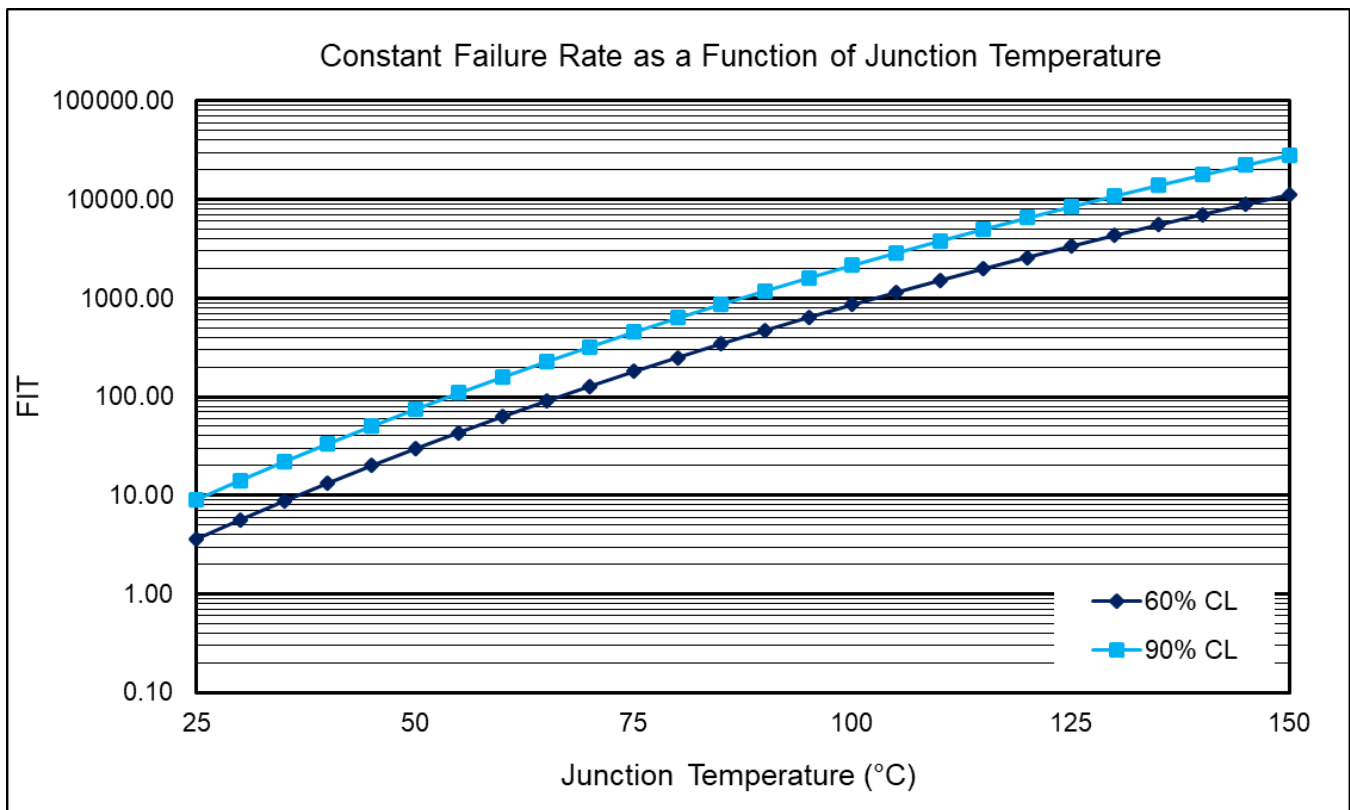
	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	1.28E+06	717.7	1.39E+06
Constant (Random)	2.66E+07	34.5	2.90E+07



45RFSOI Process Technology

Generation : 55nm 300mm wafer (C045S1E8)
 Units Tested : 272
 Product Family : mmWave

	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	1.01E+06	905.1	1.10E+06
Constant (Random)	2.11E+07	43.4	2.30E+07





Product Family Classification

Amplifiers (LNA & PA)

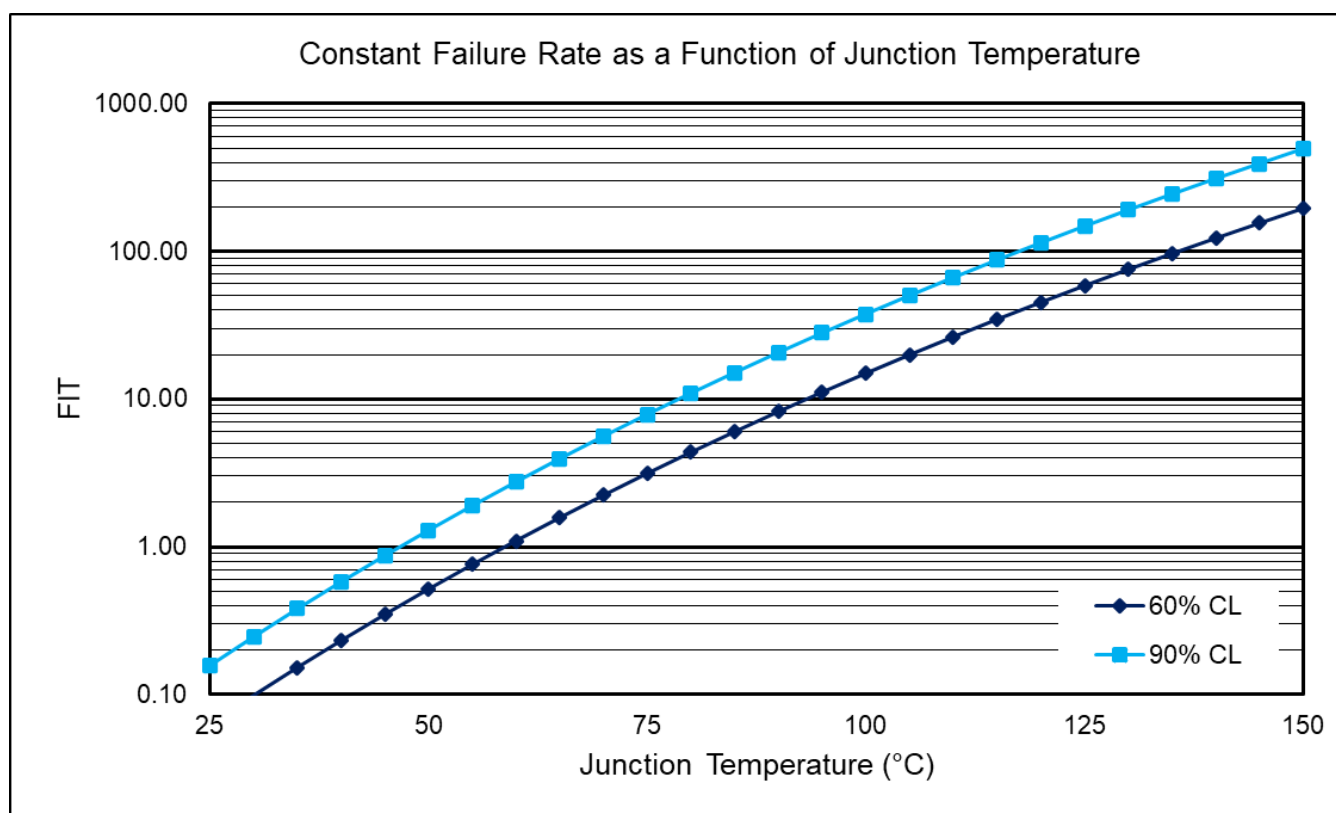
Description : UltraCMOS Low-Noise Amplifiers (LNA) and Power Amplifiers (PA)

Products in Family : See Appendix A (page 47)

Process Technology : UltraCMOS® 11, UltraCMOS® 12, UltraCMOS® 12A, UltraCMOS® 13, UltraCMOS® 13S

Units Tested : 25,786

	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	1.06E+08	8.7	1.15E+08
Constant (Random)	1.21E+09	0.8	1.32E+09



Switches (ASW, HPSW, ATS & BSW)

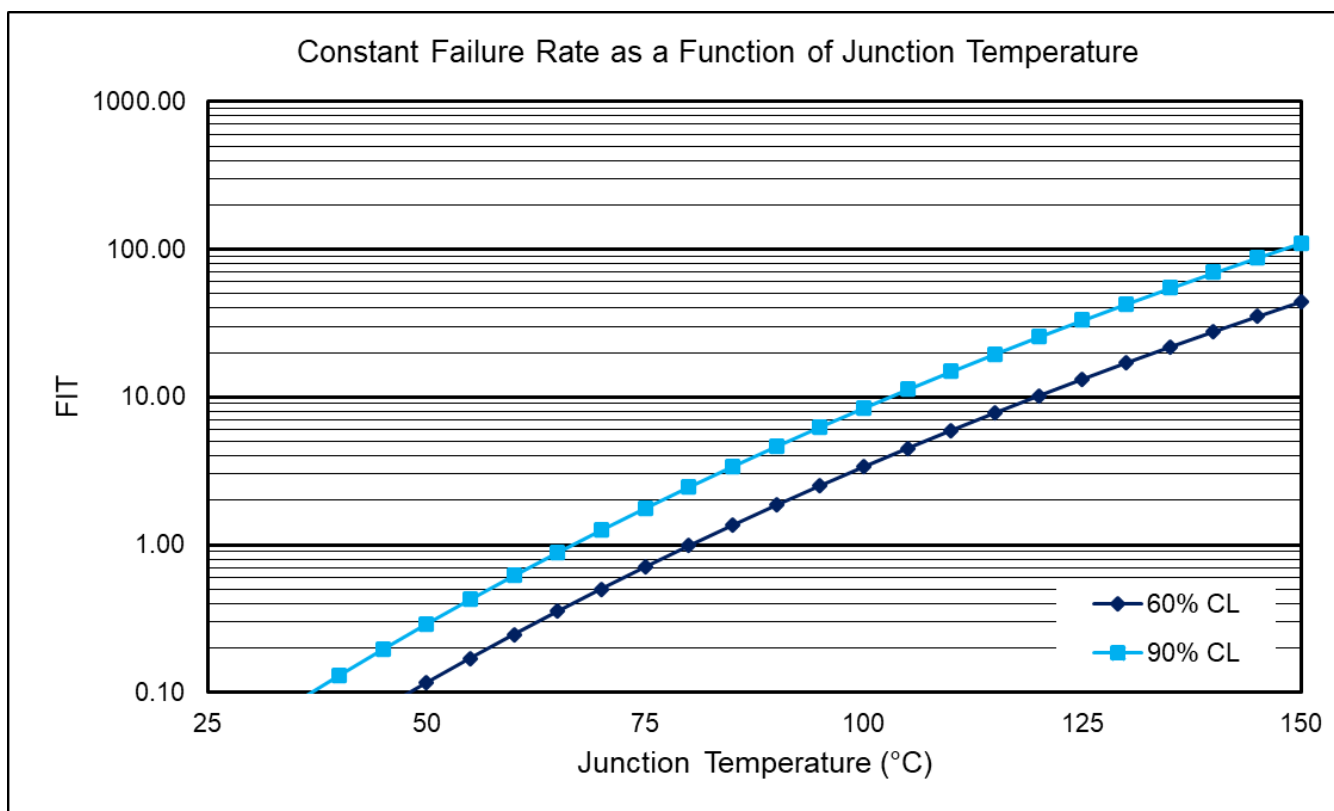
Description : Multi-pole & multi-throw high power handling antenna switch products for Mobile Wireless RF, broadband infrastructure, and Test Equipment /ATE applications.

Products in Family : See Appendix B (page 49)

Process Technology : UltraCMOS[®] 2, UltraCMOS[®] 3.5, UltraCMOS[®] 5, UltraCMOS[®] 6, UltraCMOS[®] 6.5, UltraCMOS[®] 8, UltraCMOS[®] 10, UltraCMOS[®] 11, UltraCMOS[®] 12, UltraCMOS[®] 12A, UltraCMOS[®] 13, UltraCMOS[®] 13S, UltraCMOS[®] 13SA, UltraCMOS[®] 14

Units Tested : 74,869

	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	6.26E+08	1.5	6.83E+08
Constant (Random)	5.38E+09	0.2	5.87E+09



ASIC

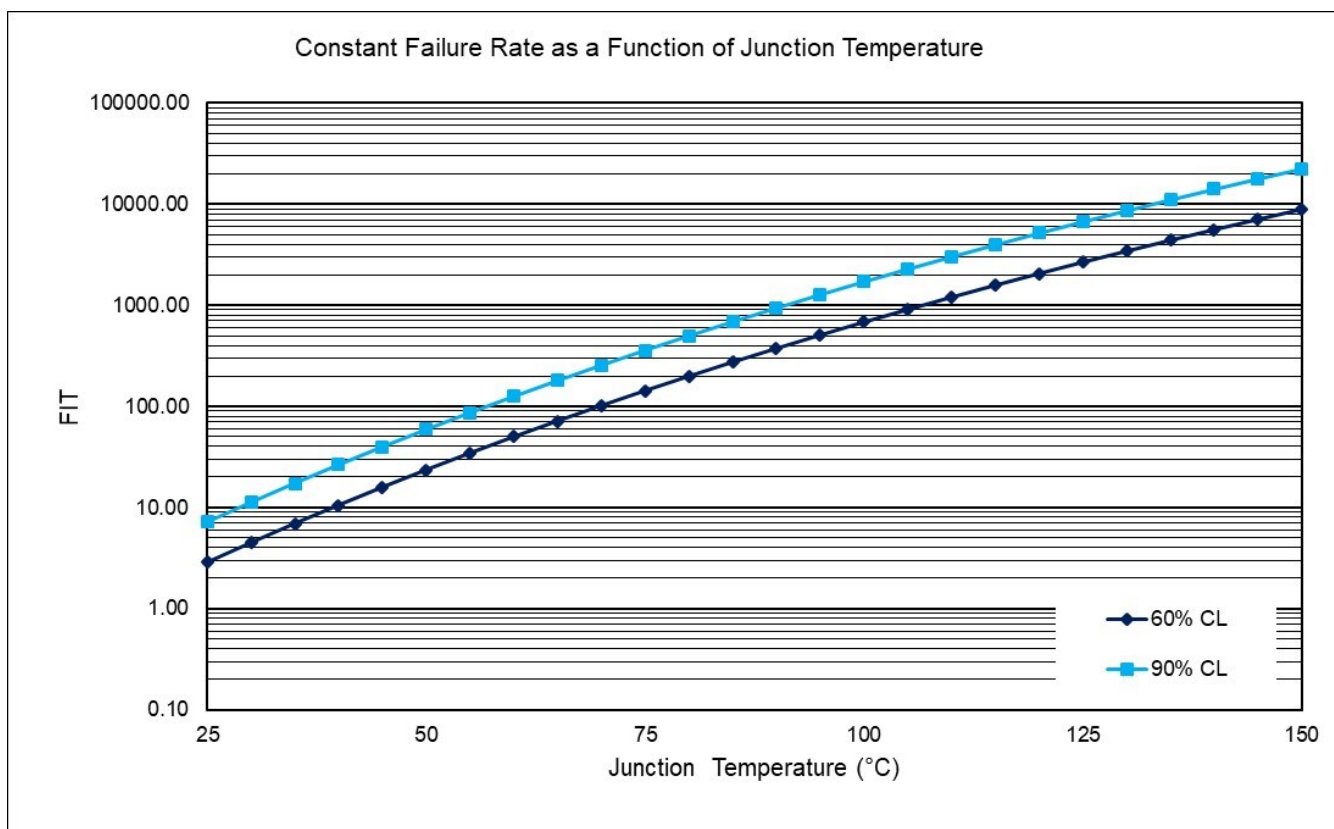
Description : These ICs have high precision ADCs for sensing MEMS capacitance and high accuracy temperature sensors to support high conversion rates and low latency.

Products in Family : WP71900, WP71901

Process Technology : 55LPx

Units Tested : 343

Standard Failure Rate Calculations at 55°C and 60% CL			
	EDH (hours)	FITs	MTTF (hours)
Early Life	1.28E+06	717.7	1.39E+06
Constant (Random)	2.66E+07	34.5	2.90E+07



DC-DC

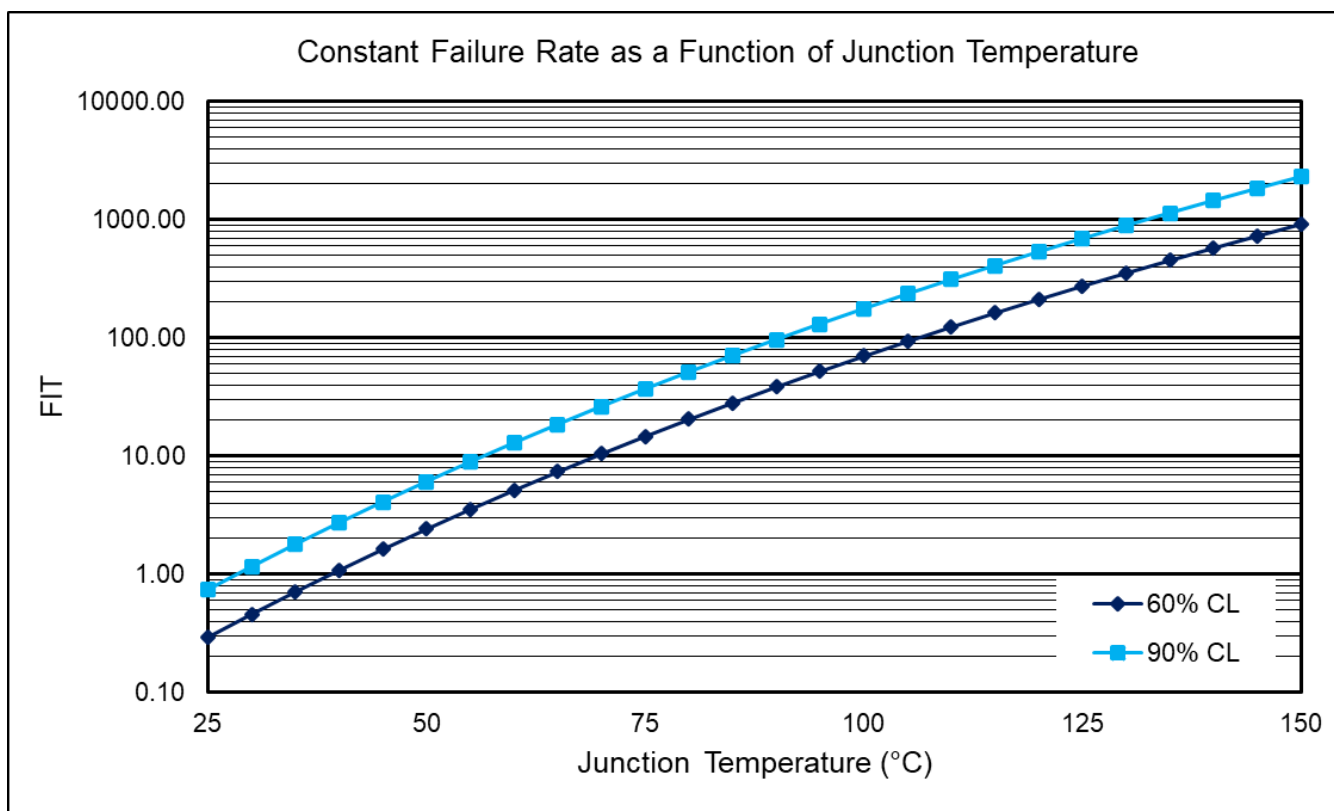
Description : These devices are ultra-high efficiency DC/DC converter solution with integrated programmable current sinks that drive strings of LEDs.

Products in Family : PE22100, PE23100, PE23108, PE23363, PE24101, PE24102, PE24103, PE25200, PE25204, PE27100, PE99151, PE99151-11, PE99153, PE99153-11, PE99155, PE99155-11

Process Technology : BCD GEN II, BCD GEN III, BCDLite, UltraCMOS® 2, UltraCMOS® 11

Units Tested : 3,782

		Standard Failure Rate Calculations at 55°C and 60% CL		
		EDH (hours)	FITs	MTTF (hours)
Early Life	Constant (Random)	1.64E+07	55.9	1.79E+07
	Constant (Random)	2.58E+08	3.6	2.82E+08



Digital Step Attenuators (DSA)

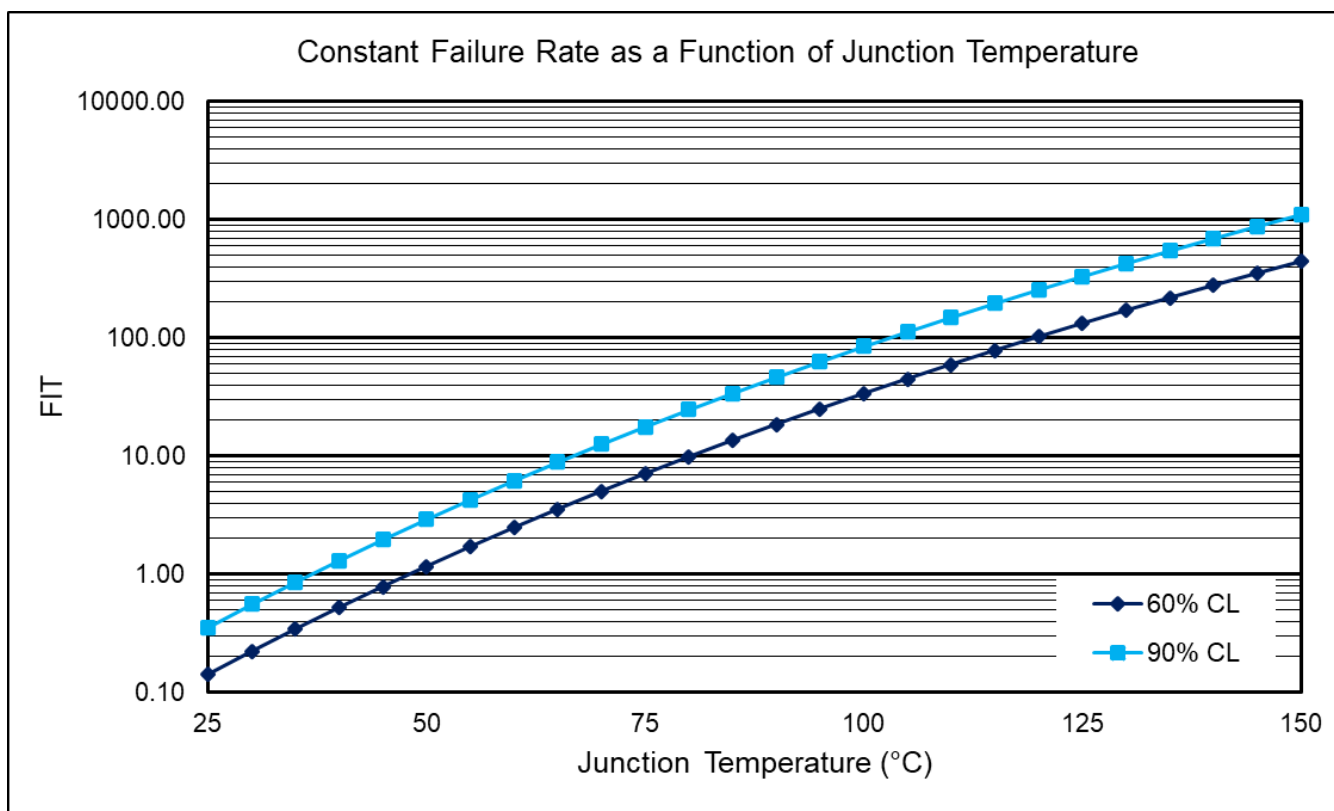
Description : 50Ω and 75Ω Digital Step Attenuators for wireless infrastructure, microwave, test equipment and high reliability space applications.

Products in Family : PE4302, PE4306, PE4308, PE4309, PE4312, PE43204, PE43205, PE43508, PE43610, PE43703, PE43704, PE43713, PE94302

Process Technology : UltraCMOS® 2, UltraCMOS® 3.5, UltraCMOS® 5, UltraCMOS® 6.5, UltraCMOS® 8, UltraCMOS® 12

Units Tested : 6,353

	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	5.05E+07	18.1	5.52E+07
Constant (Random)	5.35E+08	1.7	5.84E+08



Digitally Tunable Capacitors (DTC)

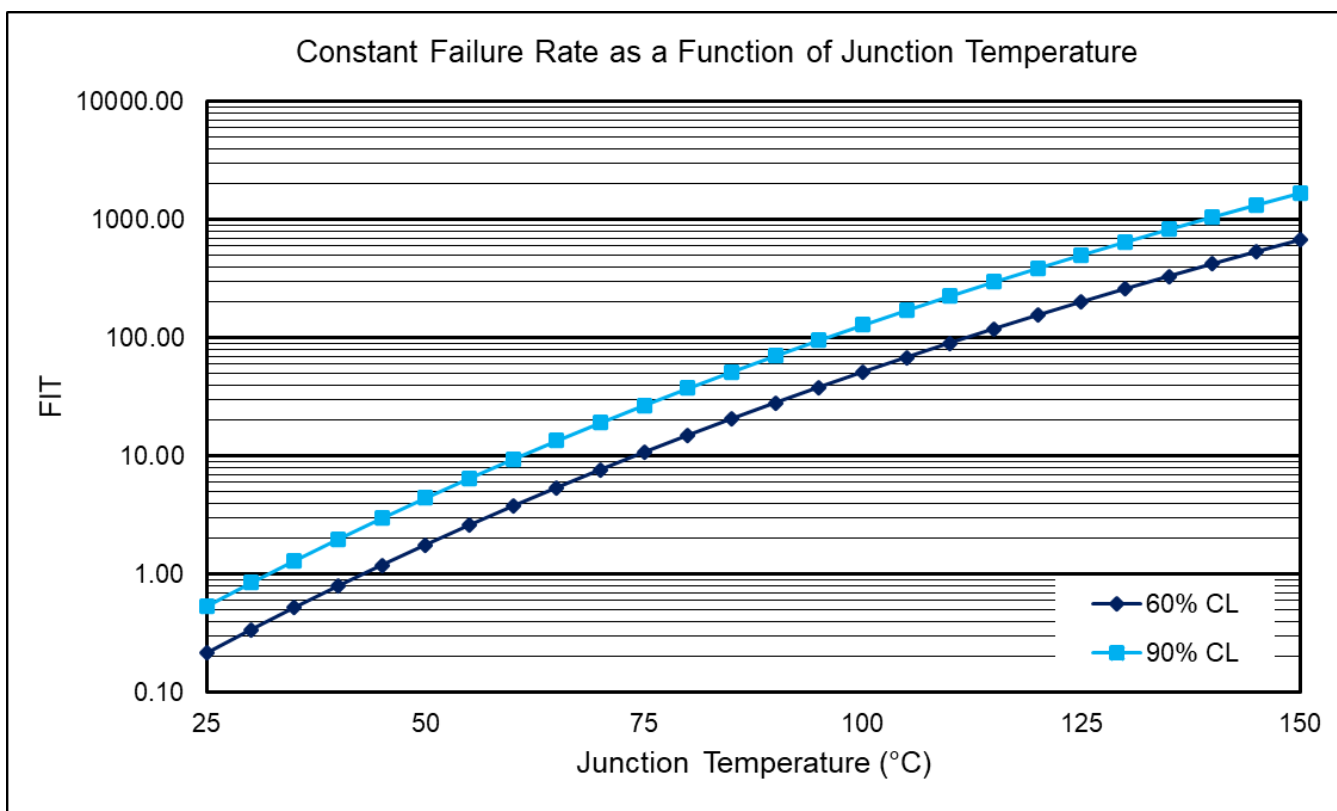
Description : Supports a wide range of tuning applications, from tuning the center frequency of mobile-TV and antennas, to tunable impedance matching and filters.

Products in Family : PE613040, PE613050, PE62304, PE62305, PE623060, PE623090, PE64102, PE64906

Process Technology : UltraCMOS® 3.5, UltraCMOS® 5, UltraCMOS® 8

Units Tested : 2,885

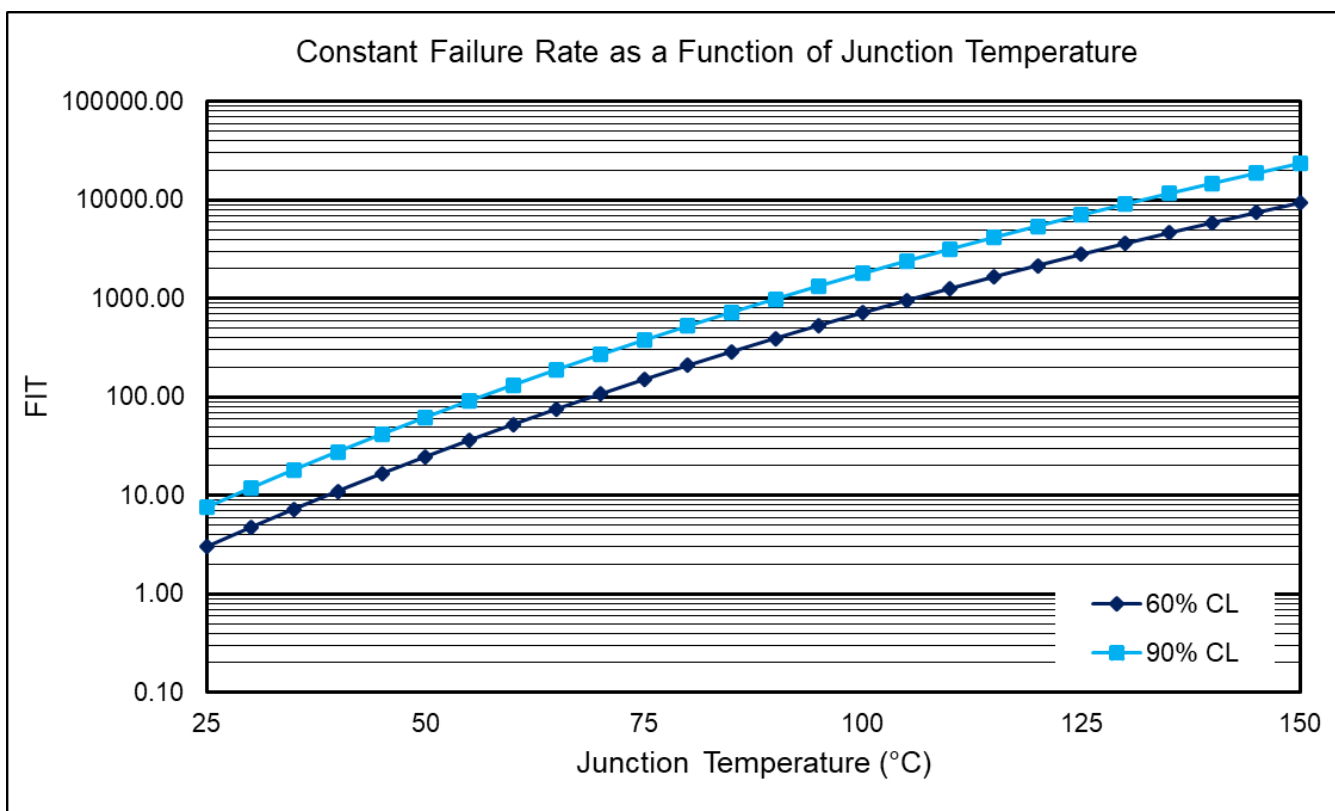
		Standard Failure Rate Calculations at 55°C and 60% CL		
		EDH (hours)	FITs	MTTF (hours)
Early Life Constant (Random)		3.38E+07	27.1	3.68E+07
		3.53E+08	2.6	3.85E+08



GaN Driver Product Family

Description : High-speed FET Driver
 Products in Family : PE29100, PE29101, PE29102
 Process Technology : UltraCMOS® 6.5, UltraCMOS® 8
 Units Tested : 327

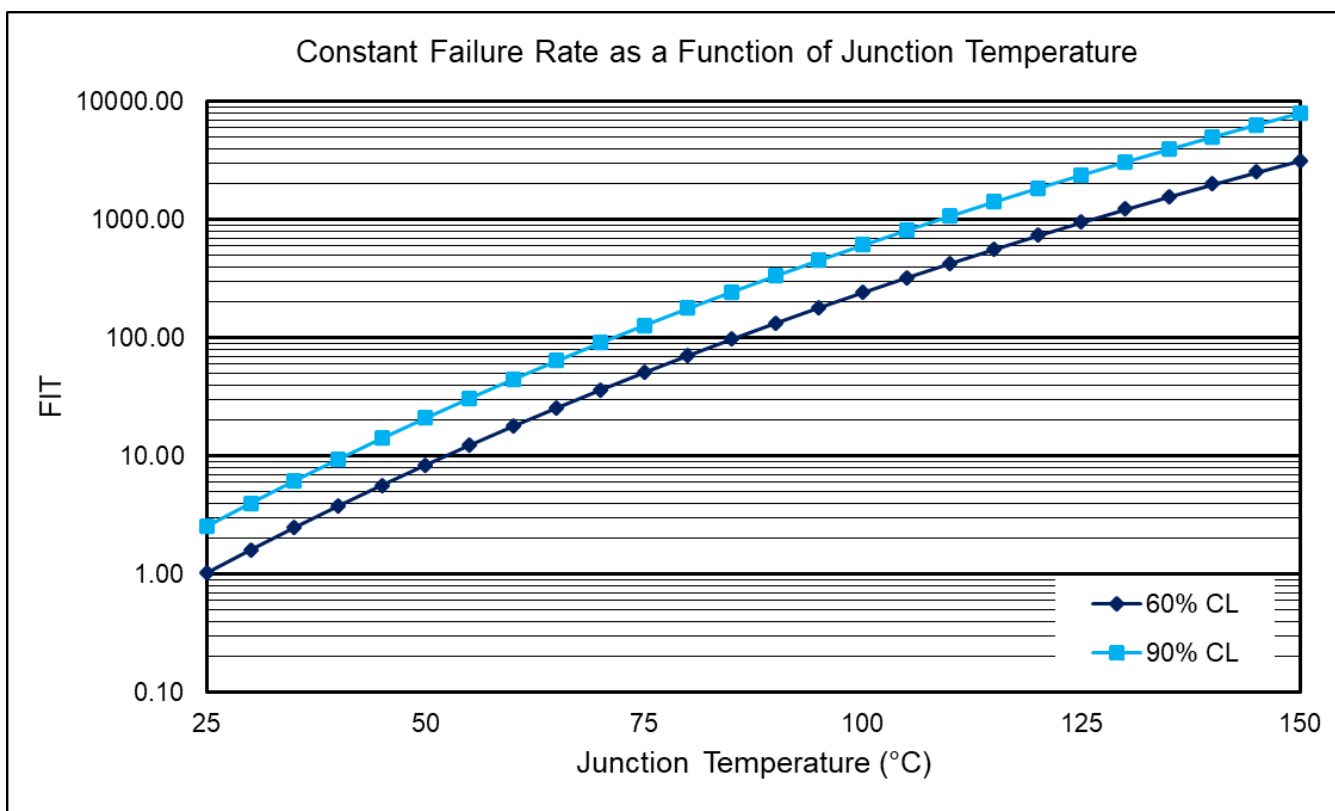
		Standard Failure Rate Calculations at 55°C and 60% CL		
		EDH (hours)	FITs	MTTF (hours)
Early Life Constant (Random)		1.22E+06	752.9	1.33E+06
		2.54E+07	36.1	2.77E+07



Power Limiters (LMTR)

Description : UltraCMOS Power Limiters.
 Products in Family : PE45140, PE45361, PE45450
 Process Technology : UltraCMOS® 5, UltraCMOS® 8
 Units Tested : 589

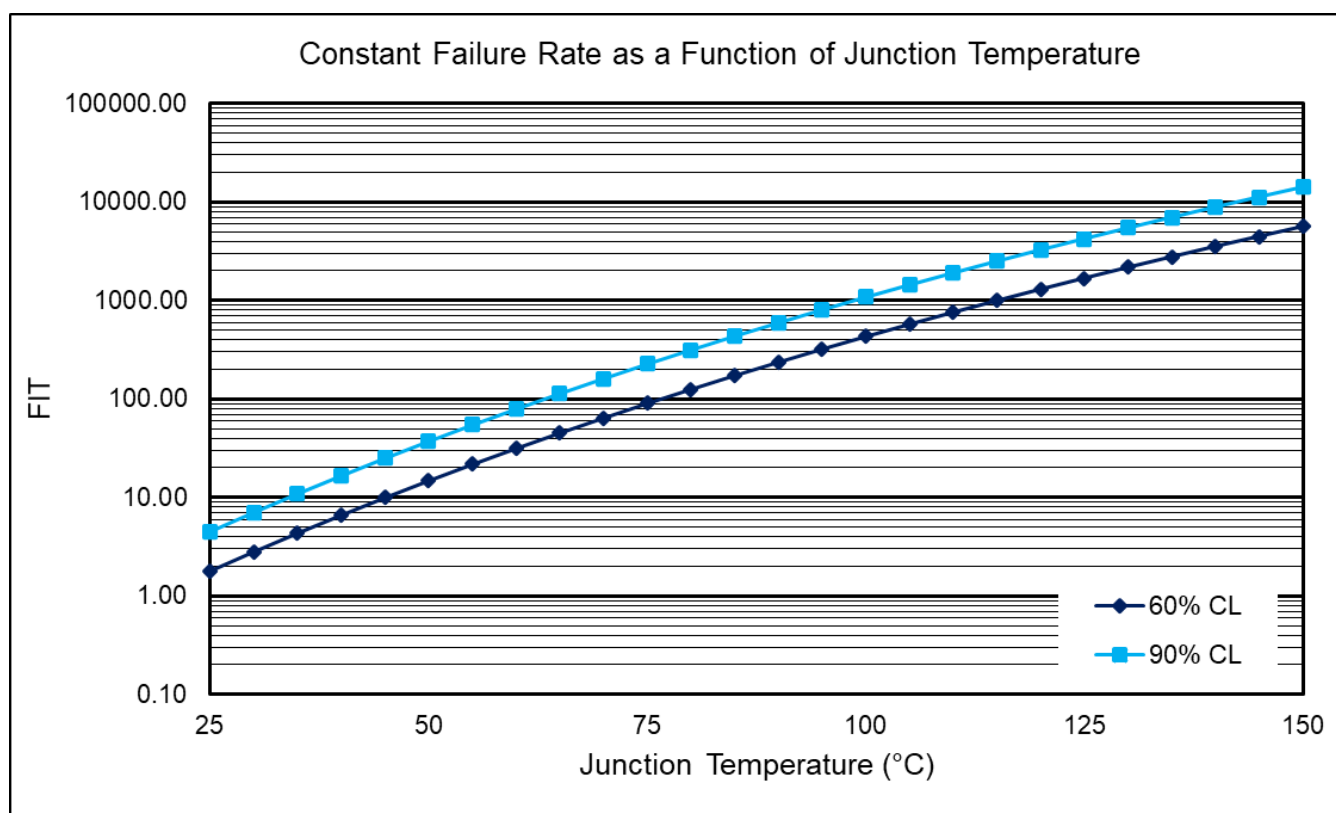
		Standard Failure Rate Calculations at 55°C and 60% CL		
		EDH (hours)	FITs	MTTF (hours)
Early Life Constant (Random)		7.04E+06	130.2	7.68E+06
		7.45E+07	12.3	8.13E+07



mmWave

Description : mmWave FEM
 Products in Family : PE188100, PE188200, PE1283x0
 Process Technology : UltraCMOS® 12A, 45RFSOI
 Units Tested : 543

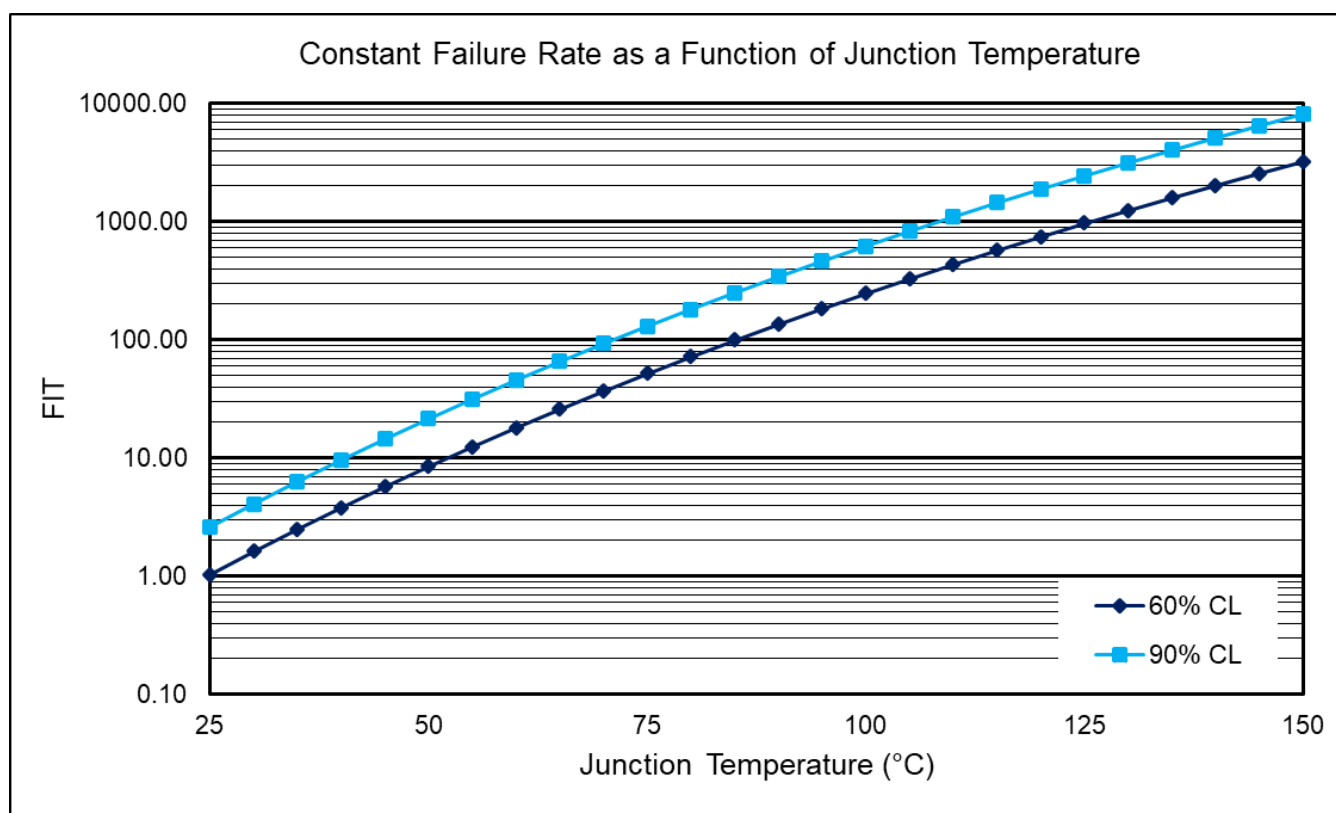
Standard Failure Rate Calculations at 55°C and 60% CL			
	EDH (hours)	FITs	MTTF (hours)
Early Life	2.02E+06	453.4	2.21E+06
Constant (Random)	4.21E+07	21.8	4.60E+07



Monolithic Phase & Amplitude Controller (MPAC)

Description : UltraCMOS RF MPACs.
 Products in Family : PE19601, PE46120, PE46130, PE46140
 Process Technology : UltraCMOS® 5, UltraCMOS® 8
 Units Tested : 565

	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	7.02E+06	130.6	7.66E+06
Constant (Random)	7.31E+07	12.5	7.98E+07



Mixers (MXR)

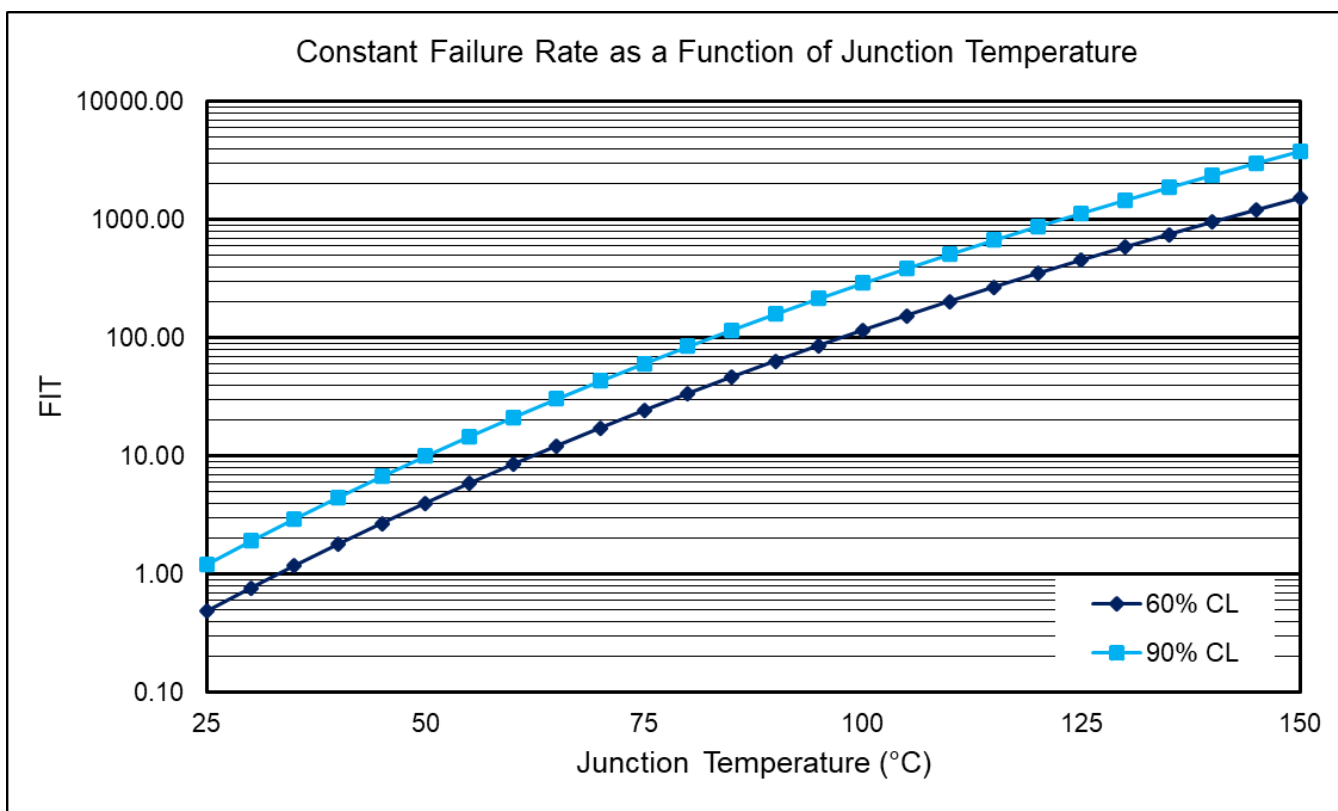
Description : UltraCMOS MOSFET quad array broadband and tuned mixers.

Products in Family : PE4120, PE4122, PE4126, PE4134, PE4140, PE4150, PE4151, PE4152, PE41901

Process Technology : UltraCMOS® 2, UltraCMOS® 8

Units Tested : 1,136

		Standard Failure Rate Calculations at 55°C and 60% CL		
		EDH (hours)	FITs	MTTF (hours)
Early Life Constant (Random)		9.15E+06	100.1	9.99E+06
		1.57E+08	5.9	1.71E+08



PA Controller (PAC)

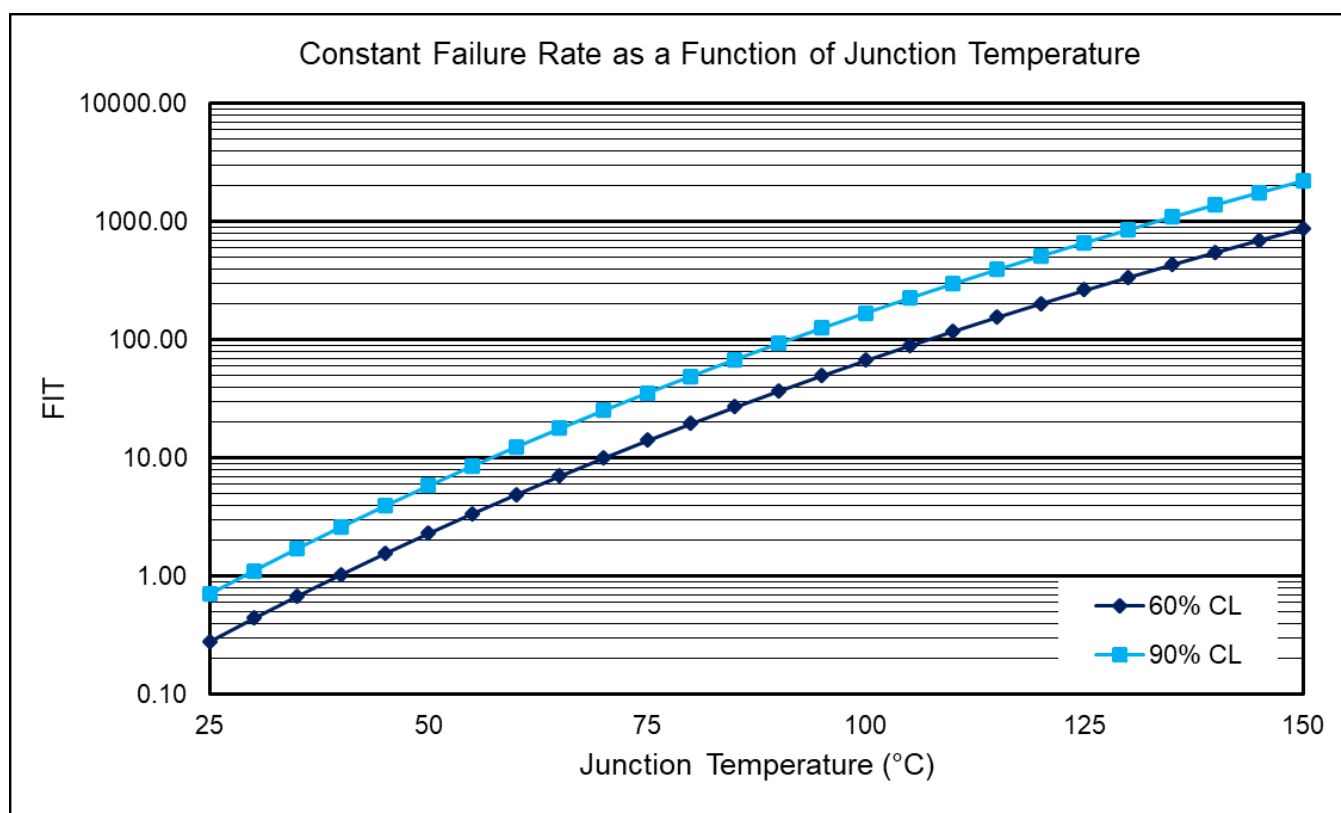
Description : PA Controller controls the PA bias current in PAD modules for RF Front Ends

Products in Family : PE510021, PE515131, PE515190, PE515200, PE51522x, PE519011

Process Technology : UltraCMOS® 12

Units Tested : 9,020

		Standard Failure Rate Calculations at 55°C and 60% CL		
		EDH (hours)	FITs	MTTF (hours)
Early Life Constant (Random)		3.65E+07	25.1	3.99E+07
		2.69E+08	3.4	2.93E+08



Phase Locked-Loop Synthesizers (PLL)

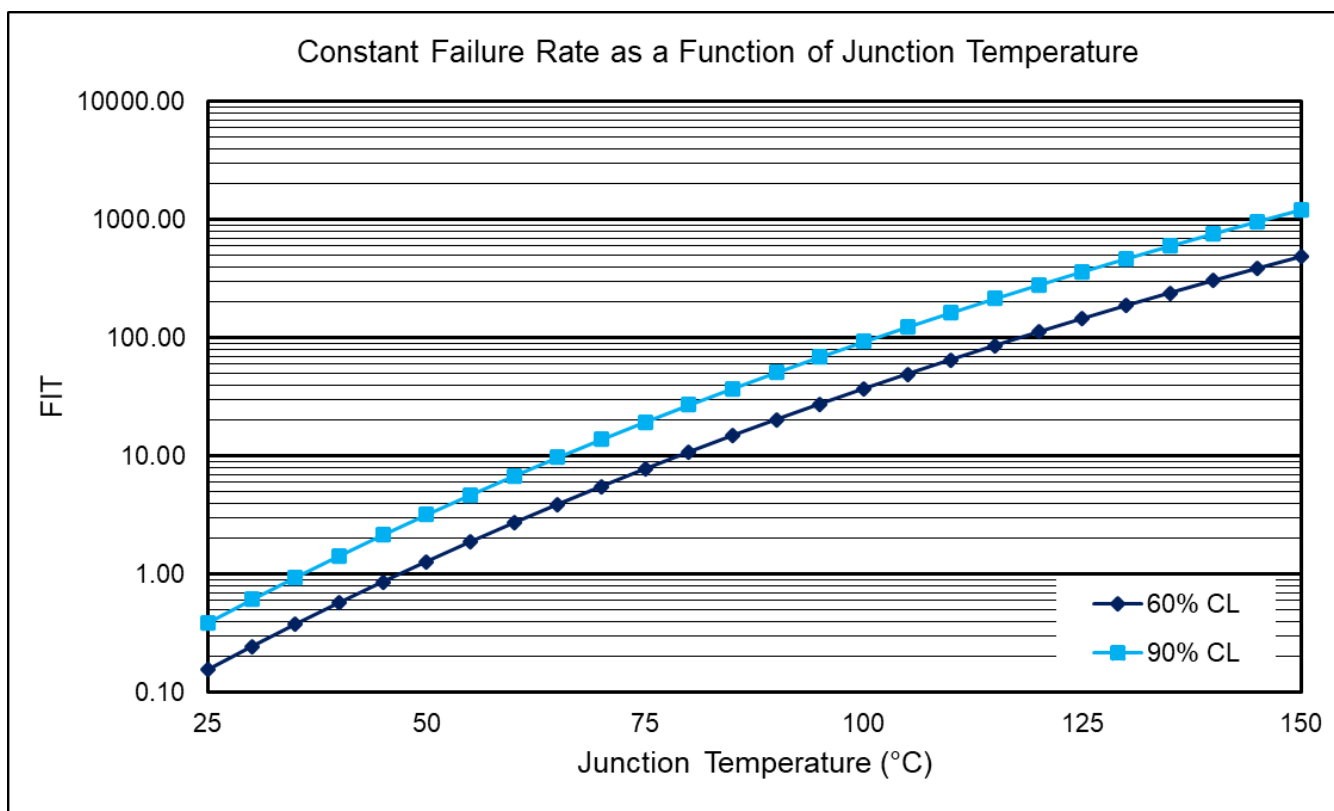
Description : Integer-N, Fractional-N and Delta Sigma Modulated frequency synthesizers for base station, mobile wireless and high reliability space applications.

Products in Family : PE3236, PE33241, PE3335, PE3336, PE33361, PE3341, PE3342, PE34641, PE83336-21, PE9601, PE9701, PE9702, PE97022, PE9704, PE97042, PE97240, PE9763, PE9763-14, PE97632, PE97640

Process Technology : UltraCMOS® 2, UltraCMOS® 5

Units Tested : 9,269

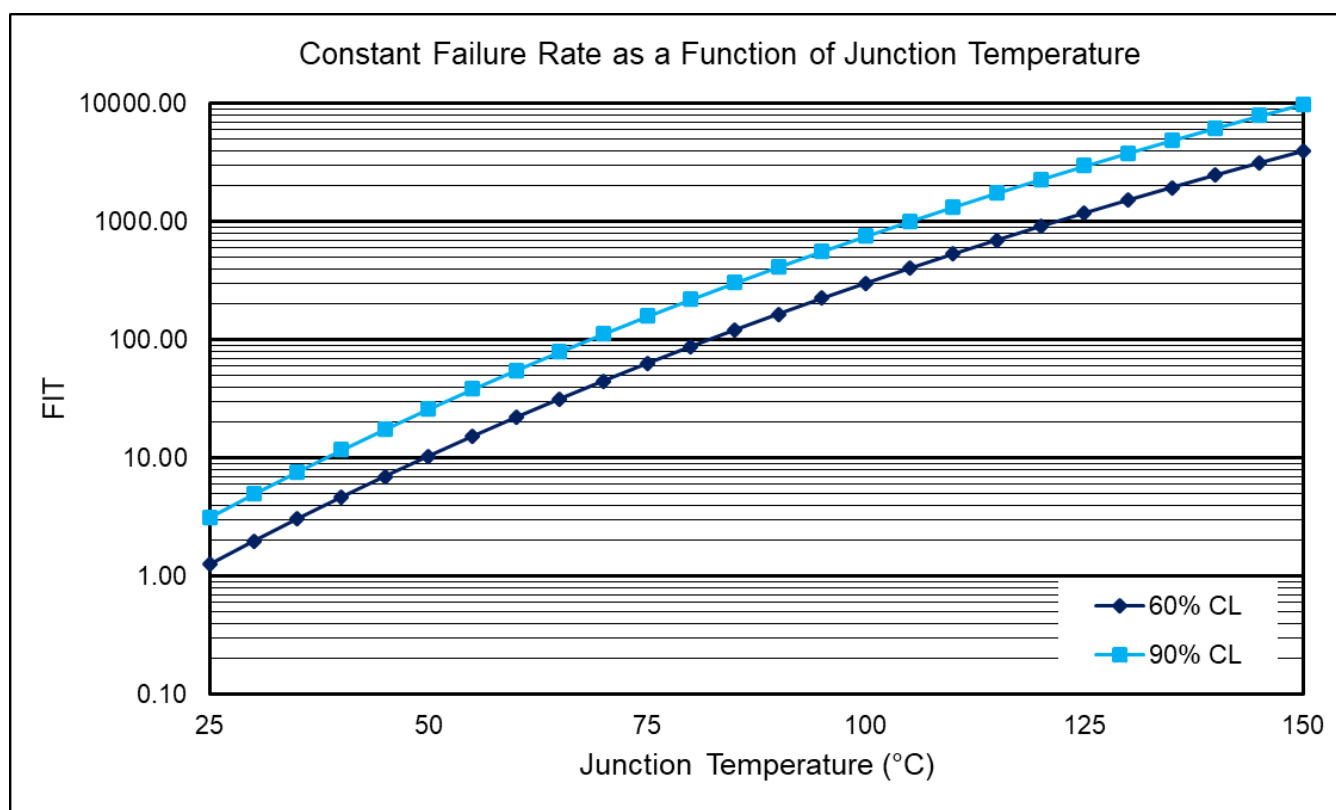
Standard Failure Rate Calculations at 55°C and 60% CL			
	EDH (hours)	FITs	MTTF (hours)
Early Life	4.54E+07	20.2	4.95E+07
Constant (Random)	4.89E+08	1.9	5.34E+08



Phase Shifters (PSH)

Description : UltraCMOS RF Phase Shifters.
 Products in Family : PE44820
 Process Technology : UltraCMOS® 5
 Units Tested : 432

	Standard Failure Rate Calculations at 55°C and 60% CL		
	EDH (hours)	FITs	MTTF (hours)
Early Life	5.37E+06	170.8	5.86E+06
Constant (Random)	6.00E+07	15.3	6.55E+07



Prescalers (PSR)

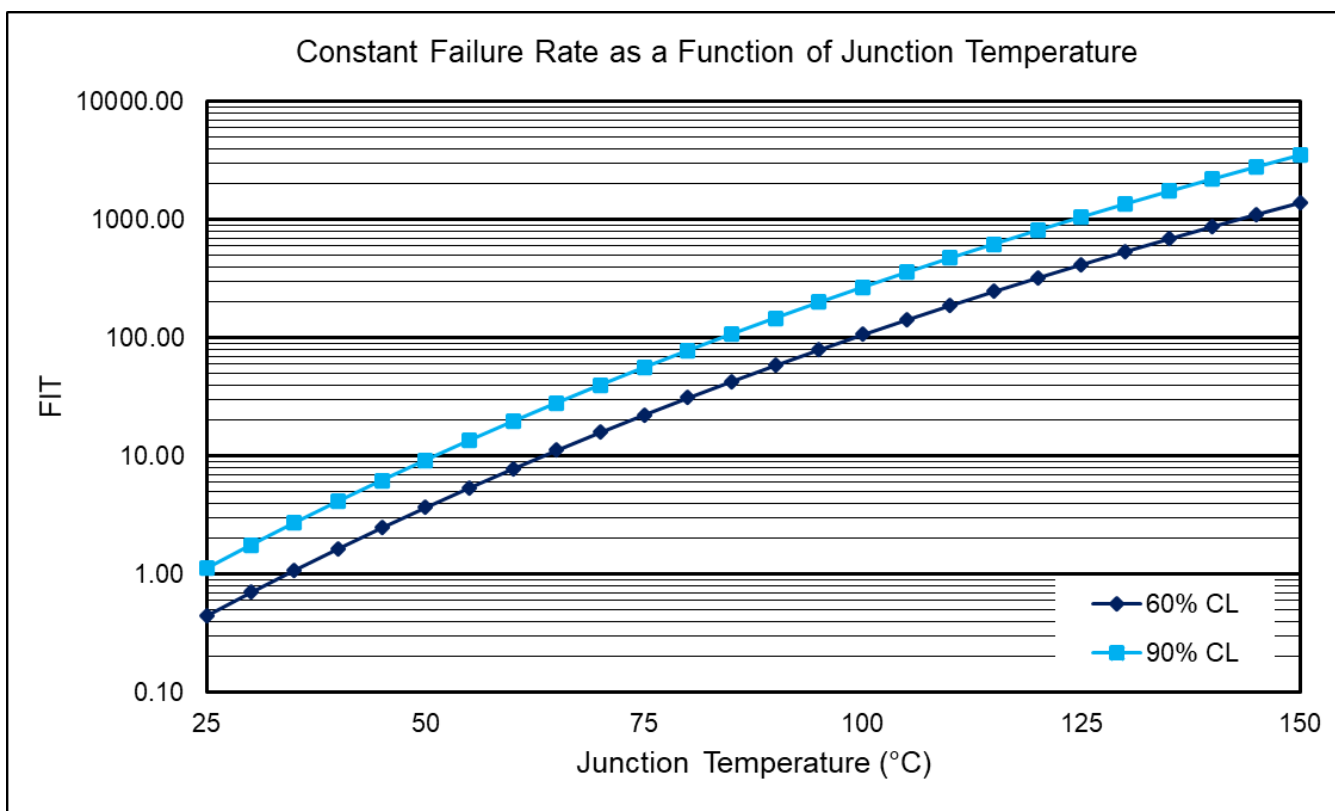
Description : UltraCMOS RF Prescalers.

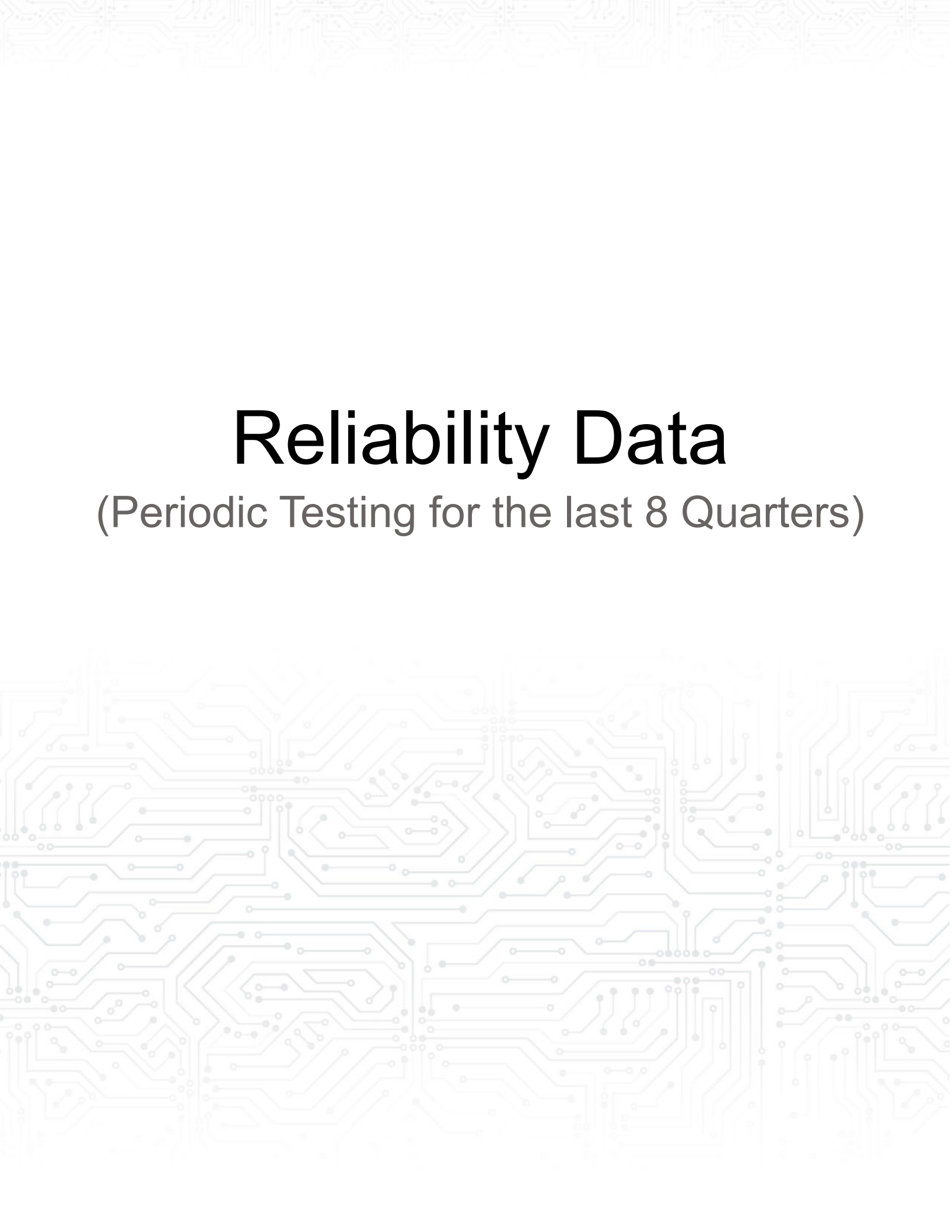
Products in Family : PE3501, PE3503, PE3511, PE3512, PE35400, PE83512, PE9301, PE9303, PE9304, PE9308, PE9309, PE9311, PE9312, PE9313

Process Technology : UltraCMOS® 2, UltraCMOS® 8

Units Tested : 2,697

Standard Failure Rate Calculations at 55°C and 60% CL			
	EDH (hours)	FITs	MTTF (hours)
Early Life	1.35E+07	68.1	1.47E+07
Constant (Random)	1.69E+08	5.4	1.85E+08



The background of the slide features a repeating pattern of a circuit board, with intricate lines and nodes in a light gray color.

Reliability Data

(Periodic Testing for the last 8 Quarters)

High Temperature Operating Life (HTOL)

Reference Standards : JESD22-A108

Test Conditions : $T_A = 125^{\circ}\text{C}$ (A) or 150°C (B)

: $V_{\text{bias}} = \text{max operating voltage}$

Test Duration (typical) : HTOL: 1,000 hrs. at (A) or 500 hrs. at (B)

ELFR: 48 hrs. at (A) or 24 hrs. at (B)

HTOL & ELFR	2021	2021	2021	2022	2022	2022	2022	2023
Process Technology	Q2	Q3	Q4	Q1	Q2	Q3	Q4	Q1
UltraCMOS® 2	0/161	0/84	0/85	0/80	0/85	0/85	-	-
UltraCMOS® 12	0/435	0/175	-	0/175	0/173	0/524	-	0/84
UltraCMOS® 13S	-	0/360	0/2,815	0/160	0/321	0/246	-	-
UltraCMOS® 11	-	-	-	-	-	-	-	-
UltraCMOS® 13SA	-	0/2,970	0/600	0/360	0/1,215	0/2,240	0/240	-
UltraCMOS® 3.5	0/164	0/85	-	0/80	0/85	0/85	0/85	-
UltraCMOS® 5	-	0/85	-	0/80	-	-	-	0/240
UltraCMOS® 12A	0/520	0/698	-	0/1,036	0/275	0/343	0/180	0/90
UltraCMOS® 13	0/179	0/270	0/85	-	-	0/90	-	0/90
UltraCMOS® 10	-	-	-	-	-	-	-	-
UltraCMOS® 8	-	-	-	-	-	-	-	-
UltraCMOS® 6	-	-	-	-	-	-	-	-
UltraCMOS® 6.5	-	-	-	-	-	-	-	0/85
UltraCMOS® 14	-	-	-	-	-	0/80	0/237	-
BCD Gen II	-	0/83	-	-	-	-	-	-
BCD Lite	0/276	-	-	-	-	-	-	-
55LPx	-	-	-	-	-	-	-	-
BCD Gen III	-	0/255	-	-	-	-	-	-
45RFSOI	-	-	-	0/240	-	-	-	-

HTOL & ELFR	2021	2021	2021	2022	2022	2022	2022	2023
Product Group	Q2	Q3	Q4	Q1	Q2	Q3	Q4	Q1
Switch	0/325	0/3,669	0/3,585	0/680	0/1,616	0/2,490	0/562	0/85
Amplifier	0/699	0/968	-	0/797	0/453	0/854	0/180	0/180
PLL	-	-	-	-	-	-	-	-
PAC	0/435	0/90	-	0/175	0/85	0/349	-	0/84
DSA	-	-	-	-	-	-	-	-
DC-DC	0/276	0/338	-	-	-	-	-	-
DTC	-	-	-	0/80	-	-	-	0/240
PSR	-	-	-	-	-	-	-	-
MXR	-	-	-	-	-	-	-	-
LMTR	-	-	-	-	-	-	-	-
MPAC	-	-	-	-	-	-	-	-
mmWave	-	-	-	0/479	-	-	-	-
PSH	-	-	-	-	-	-	-	-
ASIC	-	-	-	-	-	-	-	-
Driver	-	-	-	-	-	-	-	-

Temperature Cycle (TC)

Reference Standards : JESD22-A104

Test Conditions : -55°C to +125°C (B)

: -65°C to +150°C (C)

Test Duration (typical) : 1,000 cyc. at (B) or 500 cyc. at (C)

TC	2021	2021	2021	2022	2022	2022	2022	2023
Package Family	Q2	Q3	Q4	Q1	Q2	Q3	Q4	Q1
WLCSP	-	0/1,745	0/1,830	0/680	0/1,670	0/255	0/954	0/1,084
32L 5x5 QFN	-	0/50	-	-	-	-	-	-
20L 4x4 QFN	-	-	-	-	-	-	-	-
6L SC70	0/106	0/50	0/50	-	0/50	0/50	-	-
12L 2x2 QFN	0/101	0/55	-	0/50	0/50	0/50	0/50	-
16L 3x3 QFN	-	-	-	-	-	-	-	-
Flip Chip Die	-	-	-	-	-	-	-	0/165
32L 5x5 FCLGA	-	-	-	-	-	-	-	-
24L 4x4 QFN	-	-	-	-	-	-	-	0/50
12L 3x3 QFN	-	-	-	-	-	-	-	-
10L 2x2 FCETSLP	-	-	-	0/45	-	-	-	0/90
20L 4x4 FCLGA	0/150	-	-	-	-	-	-	-
29L 4x4 FCLGA	-	-	-	-	-	-	-	-
30L 3x3.8 QFN	-	-	-	-	-	-	-	-
8L MSOP	-	-	-	-	-	-	-	-

Note

n/a - Reliability data not available. Package (family) not yet qualified at the specified period.

dash (-) - Test not performed at the specified period.

* Plastic encapsulated packages had undergone MSL Preconditioning prior to test.

Highly Accelerated Stress Test (HAST)

Reference Standards : JESD22-A110

Test Conditions : 130°C, 85% RH, 2.27 atm. (A)
: 110°C, 85% RH, 1.20 atm. (B)

Test Duration (typical) : 96 hrs. at (A) or 264 hrs. at (B)

HAST	2021	2021	2021	2022	2022	2022	2022	2023
Package Family	Q2	Q3	Q4	Q1	Q2	Q3	Q4	Q1
WLCSP	0/150	0/660	-	-	-	0/234	0/80	0/462
32L 5x5 QFN	-	-	-	-	-	-	-	-
20L 4x4 QFN	-	-	-	-	-	-	-	-
6L SC70	0/108	0/54	0/50	-	-	0/50	-	-
12L 2x2 QFN	0/103	0/55	-	0/45	0/50	0/45	0/49	-
16L 3x3 QFN	-	-	-	-	-	-	-	-
Flip Chip Die	-	0/285	-	0/150	0/135	-	-	-
32L 5x5 FCLGA	-	-	-	-	-	-	-	-
24L 4x4 QFN	-	-	-	-	-	-	-	0/50
12L 3x3 QFN	-	-	-	-	-	-	-	-
10L 2x2 FCETSLP	-	-	-	0/45	-	-	-	0/135
20L 4x4 FCLGA	0/150	-	-	-	-	-	-	-

Note

n/a - Reliability data not available. Package (family) not yet qualified at the specified period.

dash (-) - Test not performed at the specified period. HAST may not apply to hermetic packages.

* Plastic encapsulated packages had undergone MSL Preconditioning prior to test.

High Temperature Storage (HTS)

Reference Standards : JESD22-A103

Test Conditions : Ta = 150°C

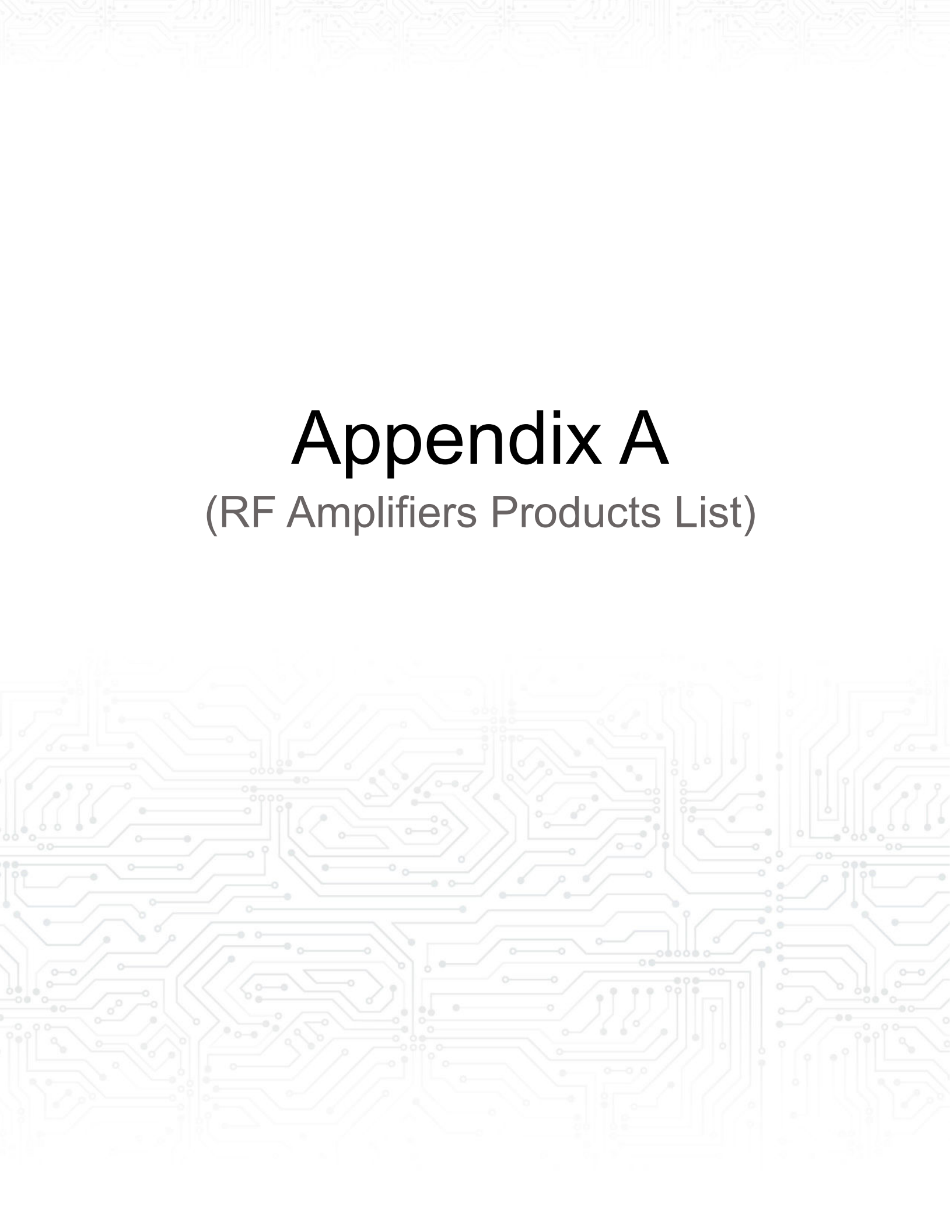
Test Duration (typical) : 1,000 hrs.

HTS	2021	2021	2021	2022	2022	2022	2022	2023
Package Family	Q2	Q3	Q4	Q1	Q2	Q3	Q4	Q1
WLCSP	-	0/495	0/170	-	0/255	0/255	0/237	0/240
32L 5x5 QFN	-	0/50	-	-	-	-	-	-
20L 4x4 QFN	-	-	-	-	-	-	-	-
6L SC70	0/167	0/50	0/50	0/50	0/50	0/50	-	-
12L 2x2 QFN	0/133	0/55	-	0/45	0/50	0/50	0/50	-
16L 3x3 QFN	-	-	-	-	-	-	-	-
Flip Chip Die	-	-	-	-	0/150	0/150	-	-
32L 5x5 FCLGA	-	-	-	-	-	-	-	-
24L 4x4 QFN	-	-	-	-	-	-	-	0/85
12L 3x3 QFN	-	-	-	-	-	-	-	-
10L 2x2 FCETSLP	-	-	-	0/45	-	-	-	0/135
20L 4x4 FCLGA	0/150	-	-	-	-	-	-	-

Note

n/a - Reliability data not available. Package (family) not yet qualified at the specified period.

dash (-) - Test not performed at the specified period.

The background of the page features a light gray, repeating pattern of circuit board traces and components, resembling a printed circuit board (PCB) layout. This pattern is visible in the top and bottom margins of the page.

Appendix A

(RF Amplifiers Products List)

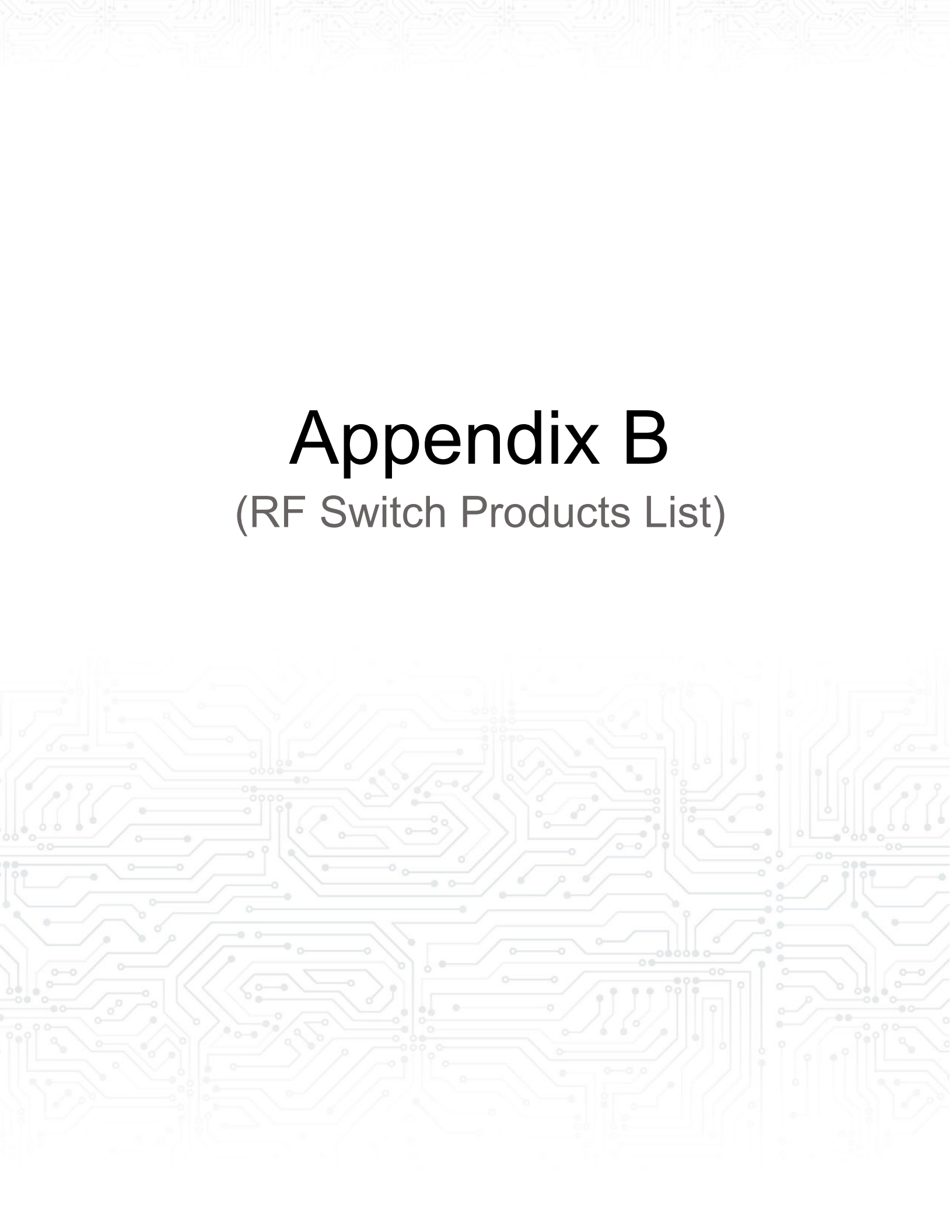
Amplifiers (LNA &PA)

Description : UltraCMOS Low-Noise Amplifiers (LNA) and Power Amplifiers (PA)

Products in Family : PE470081, PE47051x, PE471110, PE471112, PE471741, PE472110, PE477180, PE477181, PE478021, PE478031, PE478051, PE478070, PE478090, PE478091, PE478100, PE478110, PE478130, PE478140, PE478180, PE478190, PE478201, PE478211, PE47822x, PE47823x, PE479050, PE479070, PE479081, PE521200, PE521221, PE523211, PE523212, PE523231, PE525211, PE53210

Process Technology : UltraCMOS[®] 11, UltraCMOS[®] 12, UltraCMOS[®] 12A, UltraCMOS[®] 13, UltraCMOS[®] 13S

Units Tested : 25,786



Appendix B

(RF Switch Products List)

Switches (ASW, HPSW, ATS & BSW)

Description	: Multi-pole & multi-throw high power handling antenna switch products for Mobile Wireless RF, broadband infrastructure, and Test Equipment /ATE applications.
Products in Family	: PE420011, PE42020, PE420540, PE420551, PE420560, PE4210, PE421080, PE42112, PE421130, PE421141, PE421160, PE421230, PE421240, PE421261, PE421281, PE421292, PE421293, PE421294, PE421321, PE421422, PE421451, PE421453, PE421454, PE421460, PE421510, PE421550, PE421592, PE421603, PE421628, PE42164x, PE421690, PE421711, PE421729, PE421752, PE421812, PE421821, PE421880, PE421941, PE421951, PE421979, PE422020, PE4230, PE4231, PE4232, PE423422, PE423424, PE4235, PE42359, PE423641, PE4237, PE4239, PE42412, PE42420, PE42421, PE42422, PE42430, PE4244, PE42441, PE42443, PE42450, PE4251, PE42510, PE42520, PE42524, PE42525, PE42540, PE42542, PE42552, PE42556, PE4256, PE4257, PE4259, PE4261, PE426140, PE42615, PE4263, PE42633, PE426331, PE42641, PE426412, PE426482, PE42650, PE42660, PE42672, PE426810, PE42682, PE426823, PE426850, PE426860, PE426880, PE426882, PE42691, PE426911, PE42695, PE42696, PE426960, PE426970, PE4270, PE42721, PE42723, PE42742, PE42750, PE42820, PE42823, PE42850, PE429002, PE429011, PE429561, PE429570, PE4314, PE43711, PE612030, PE612033, PE612934, PE612935, PE61293x, PE613010, PE614030, PE614036, PE614910, PE614912, PE614932, PE61493x, PE615030, PE61503x, PE636030, PE636040, PE84140, PE84244, PE926C31,
Process Technology	: UltraCMOS® 2, UltraCMOS® 3.5, UltraCMOS® 5, UltraCMOS® 6, UltraCMOS® 6.5, UltraCMOS® 8, UltraCMOS® 10, UltraCMOS® 11, UltraCMOS® 12, UltraCMOS® 12A, UltraCMOS® 13, UltraCMOS® 13S, UltraCMOS® 13SA, UltraCMOS® 14
Units Tested	: 74,869